

FIG. 2

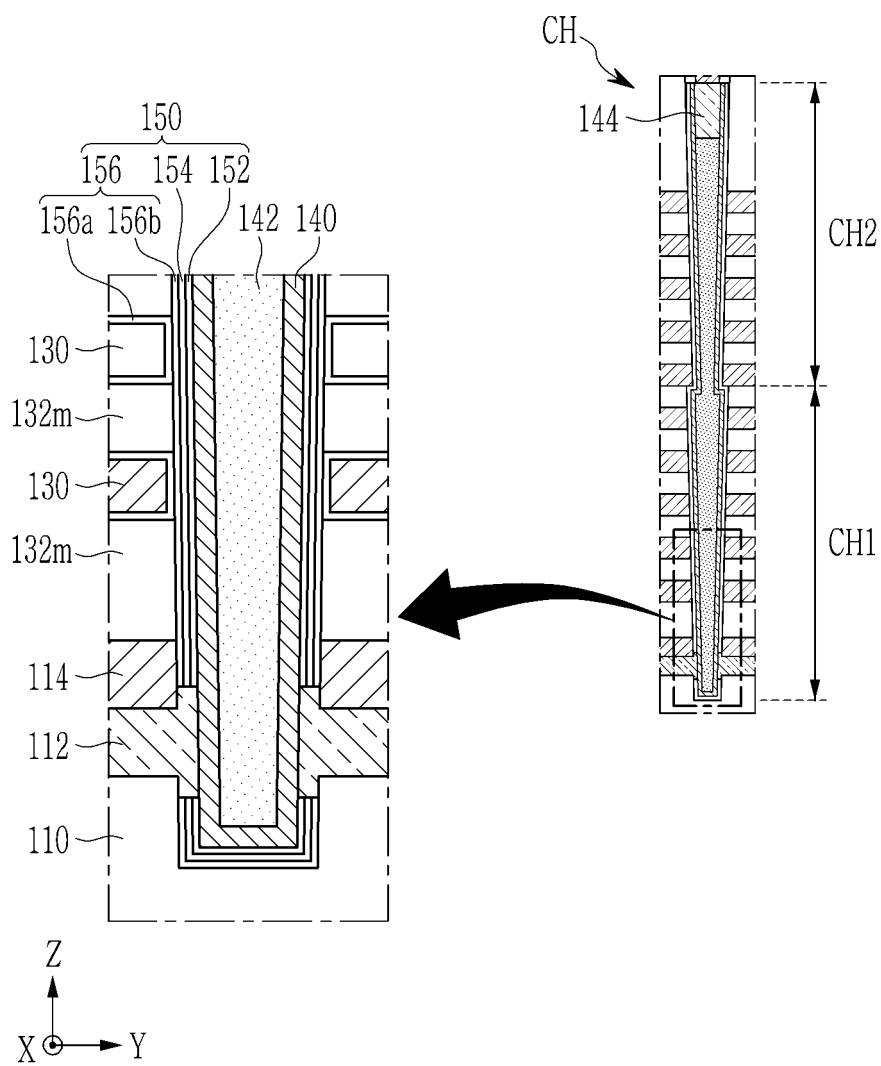


FIG. 3

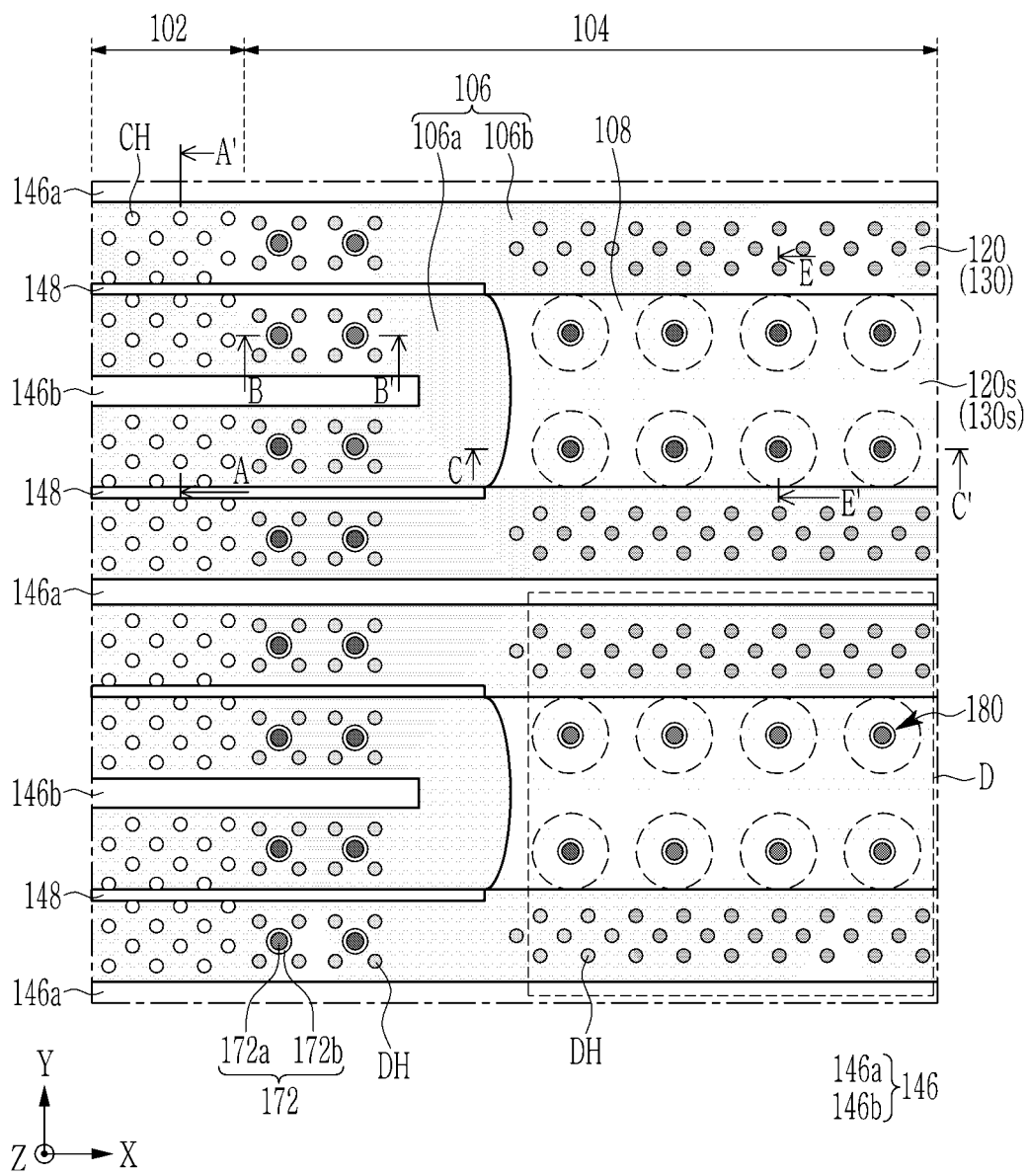


FIG. 4

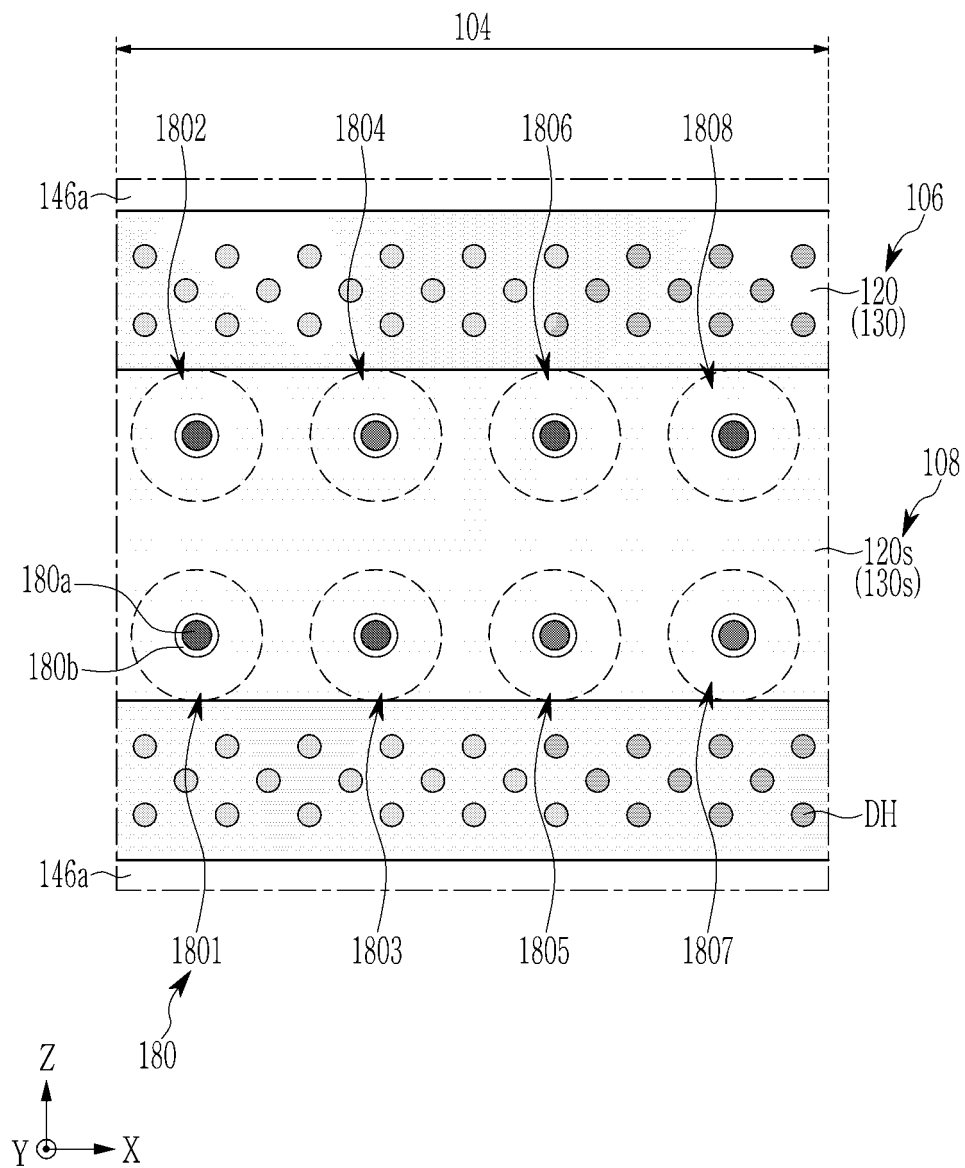


FIG. 5

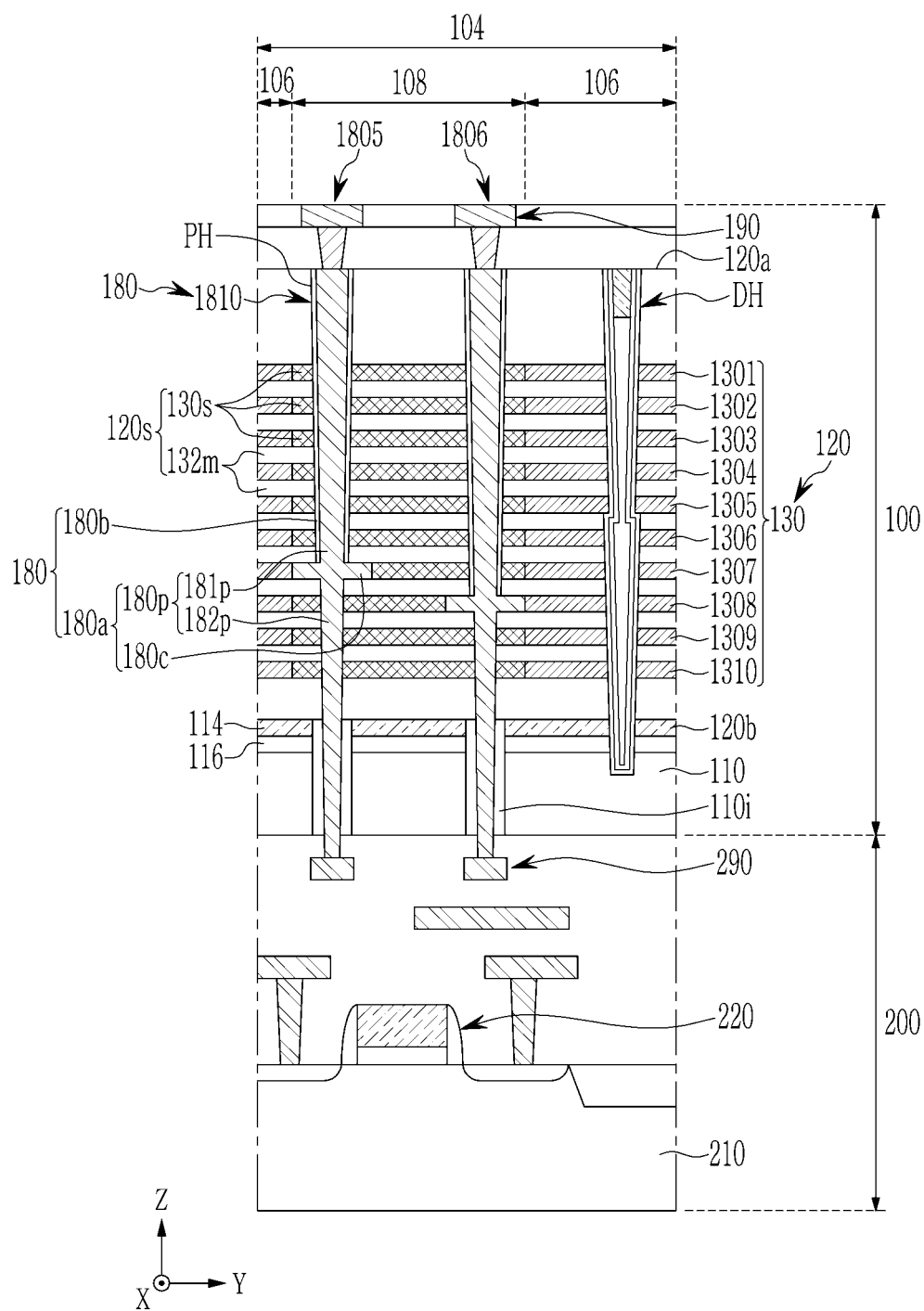


FIG. 6

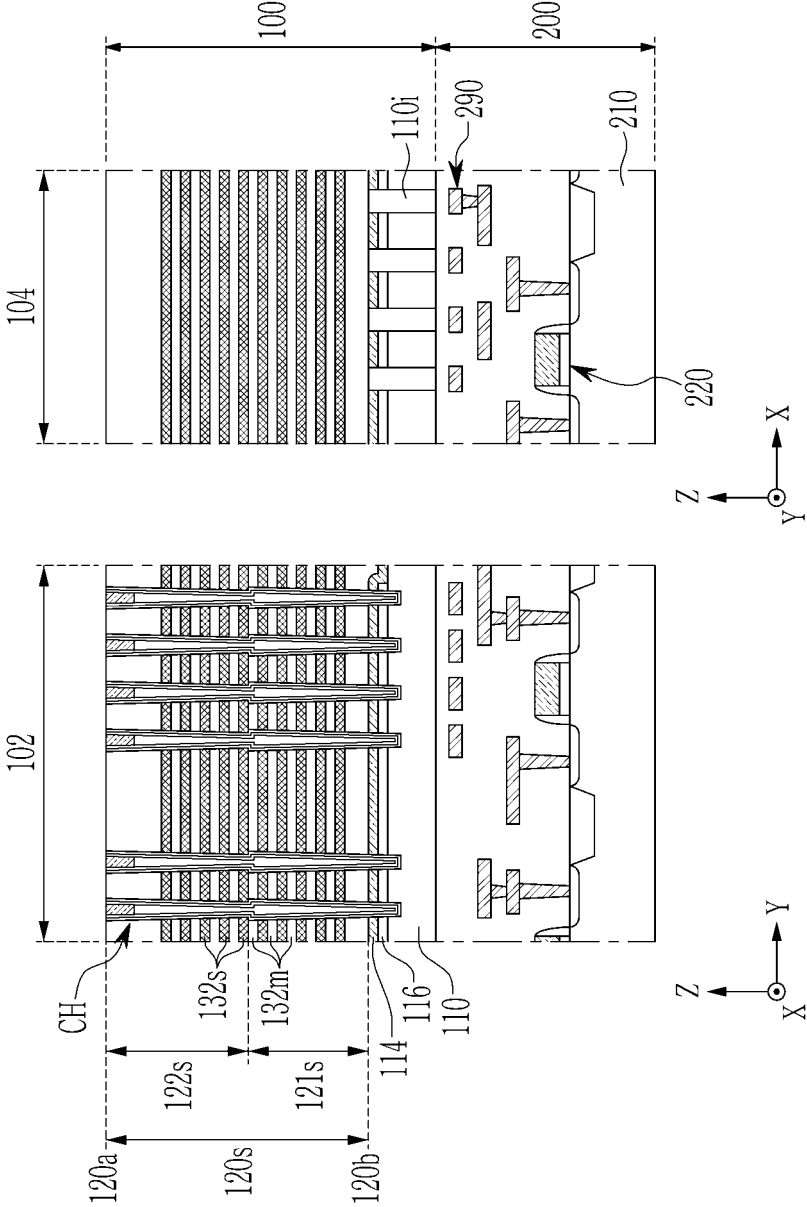


FIG. 7

E1

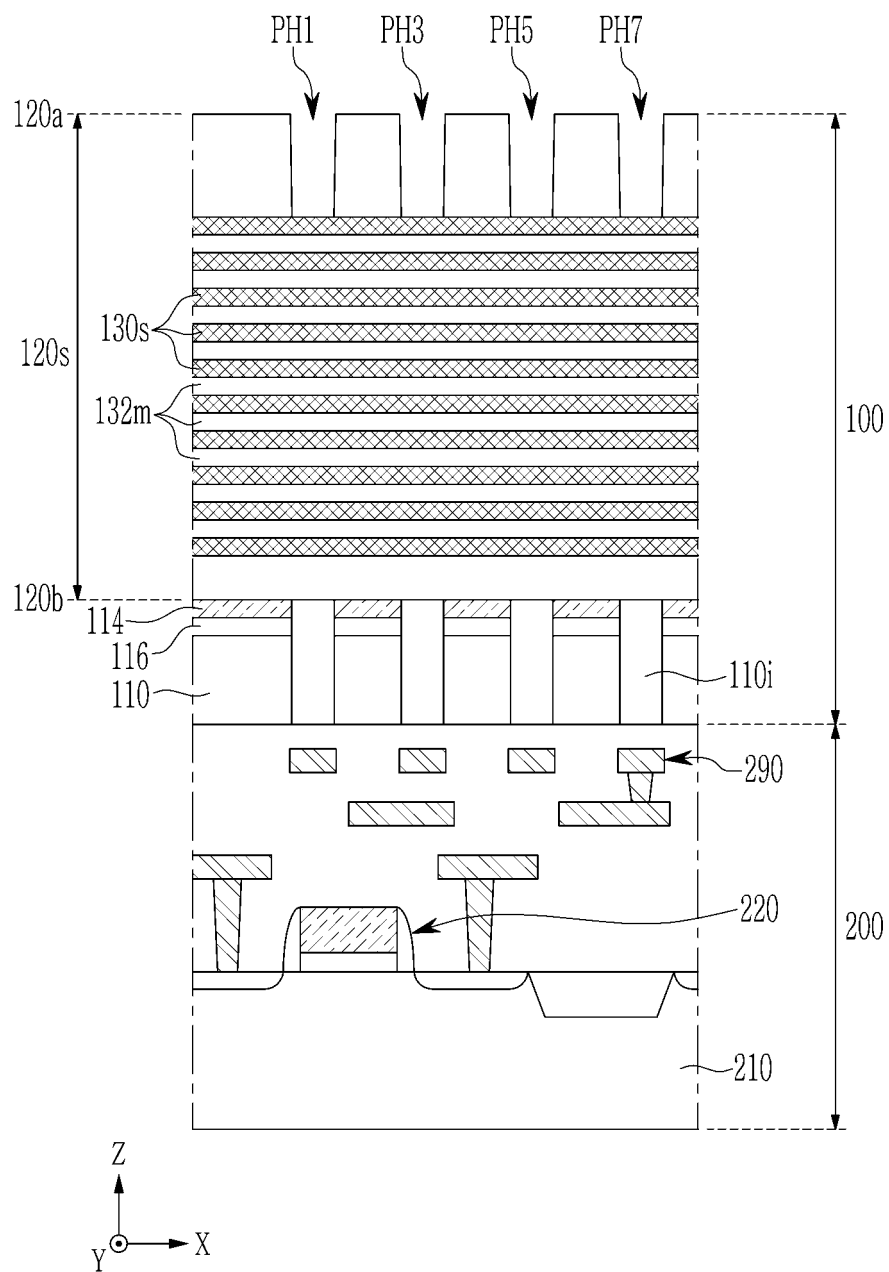


FIG. 8

E2

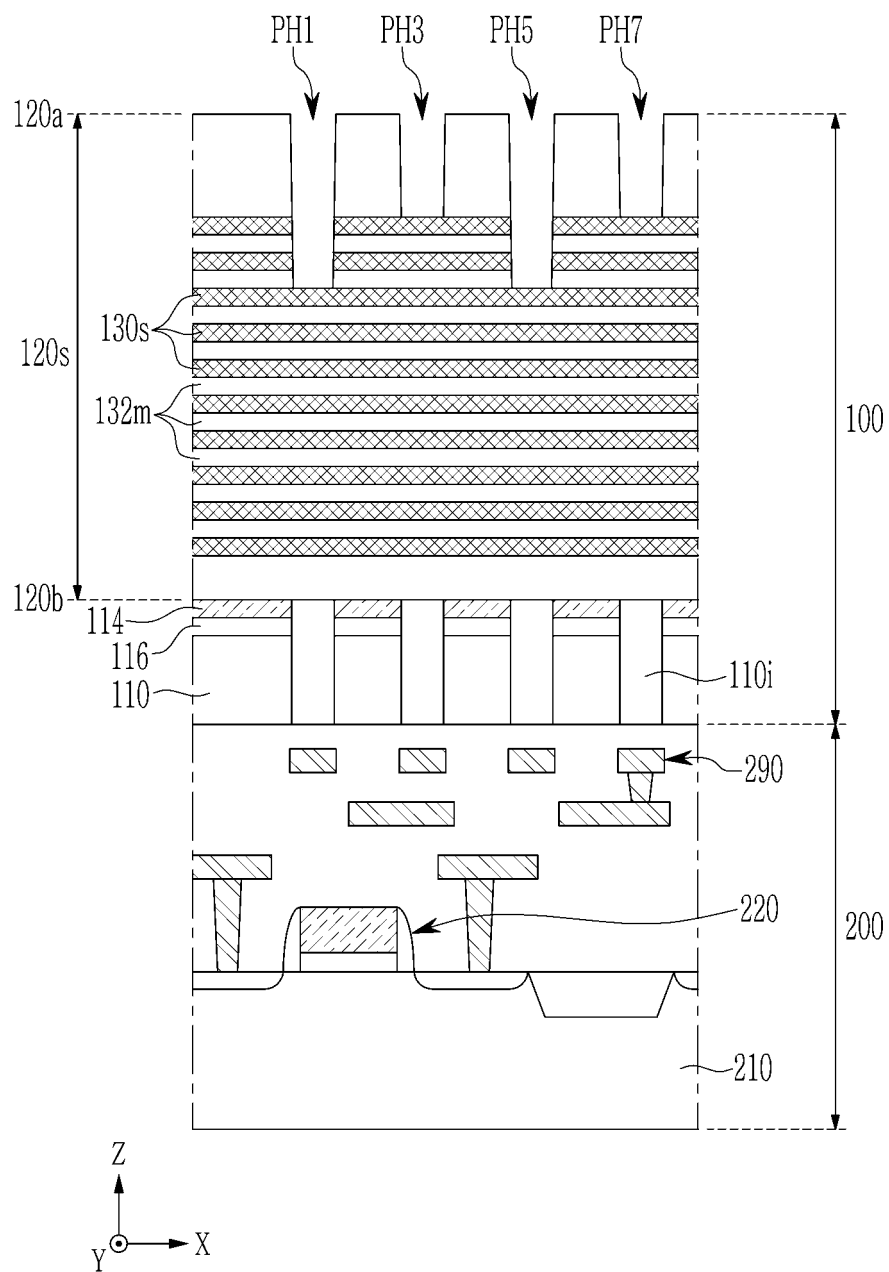


FIG. 9

E3

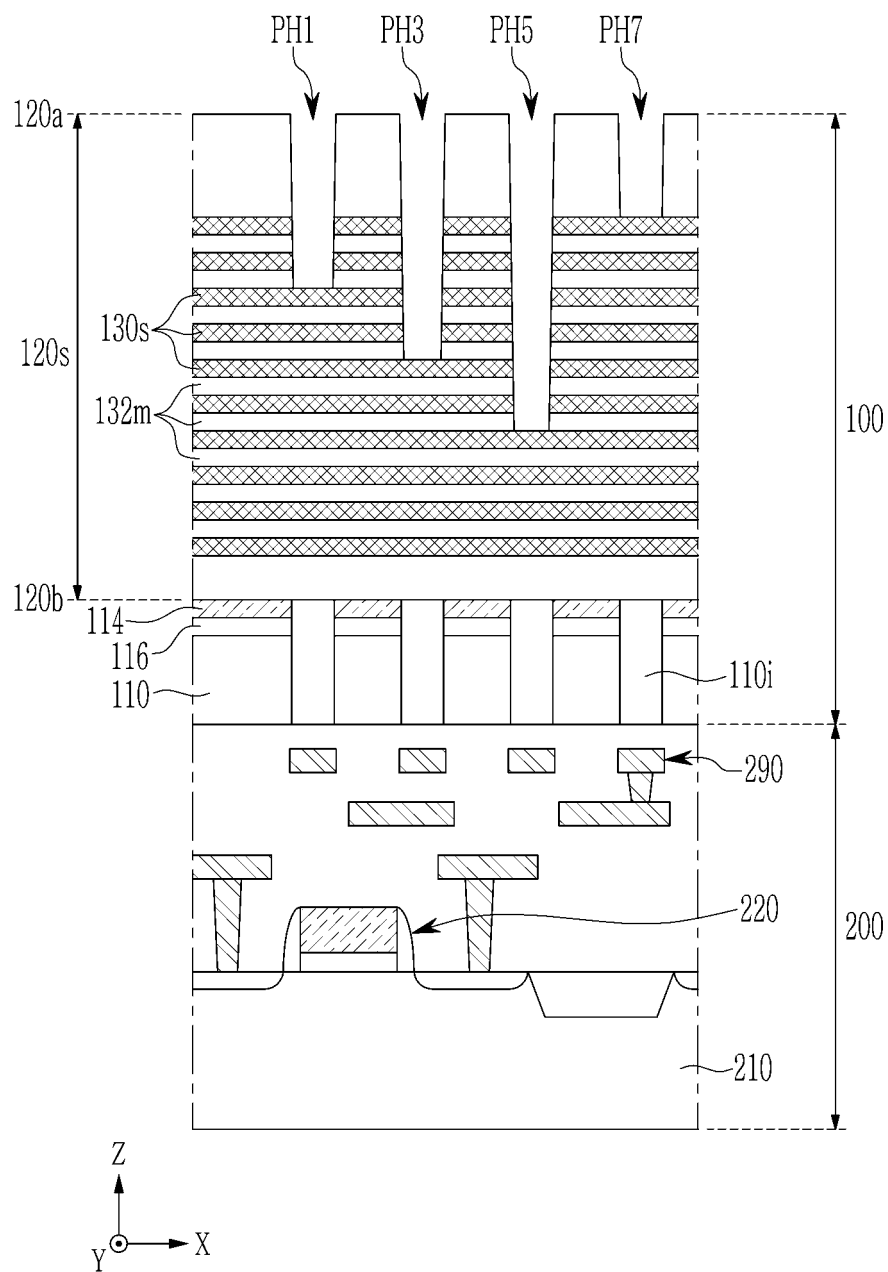


FIG. 10

E4

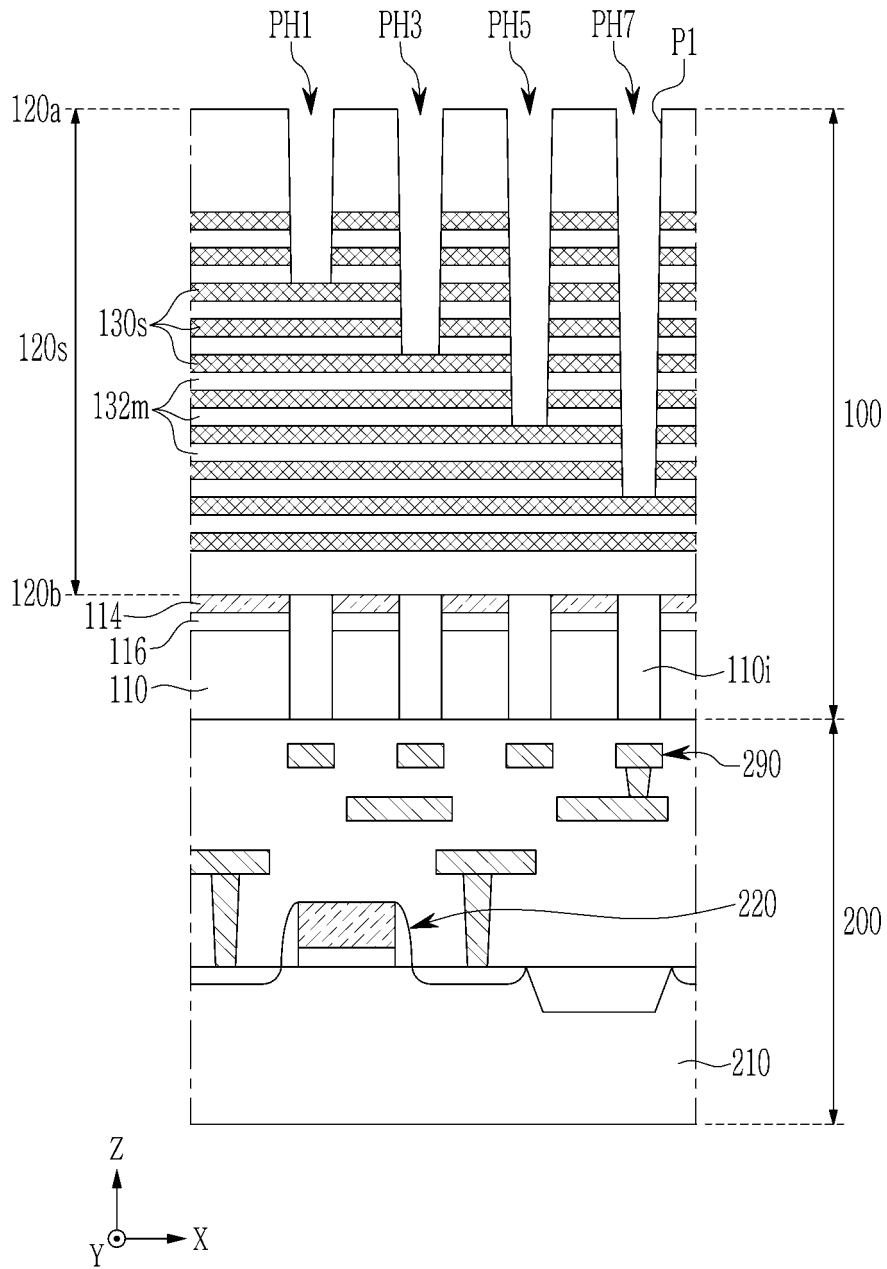


FIG. 11

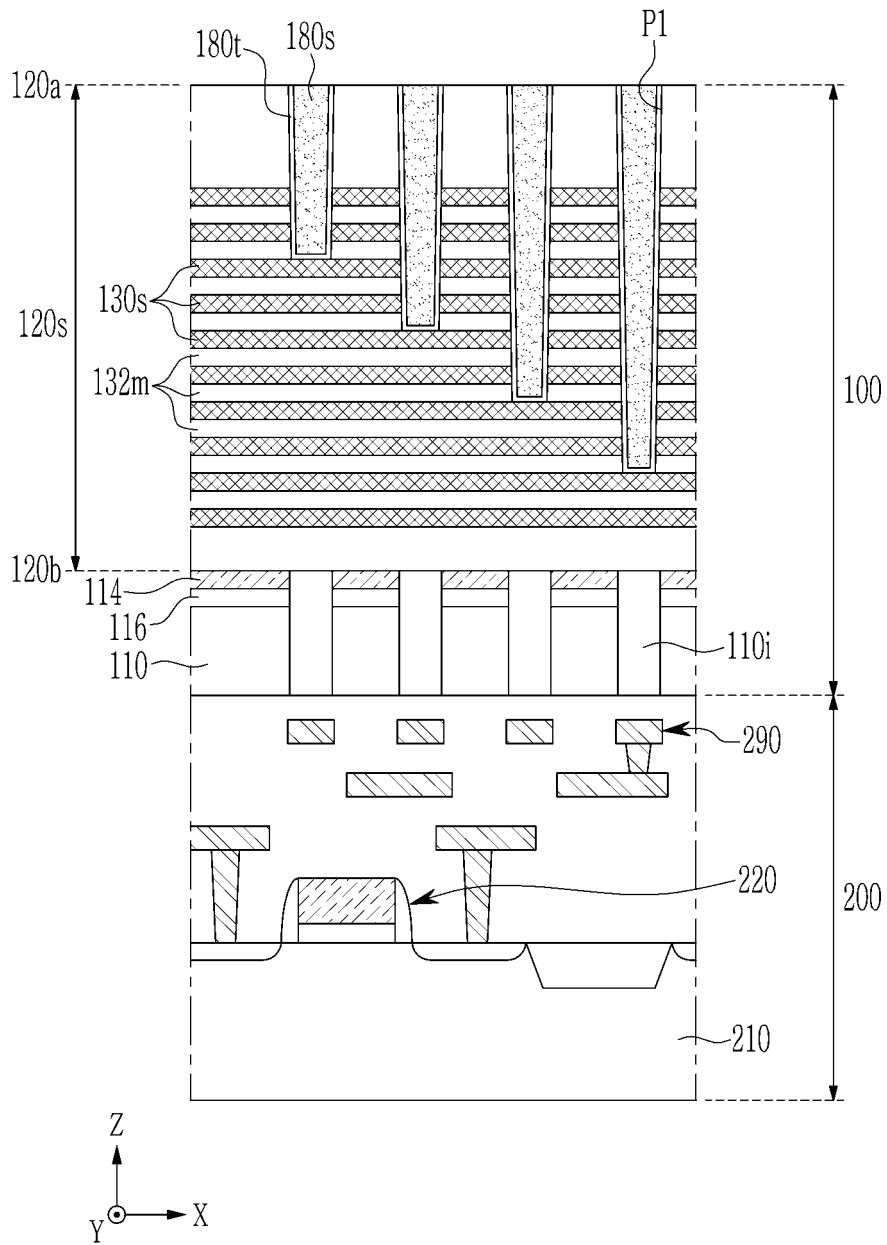


FIG. 12

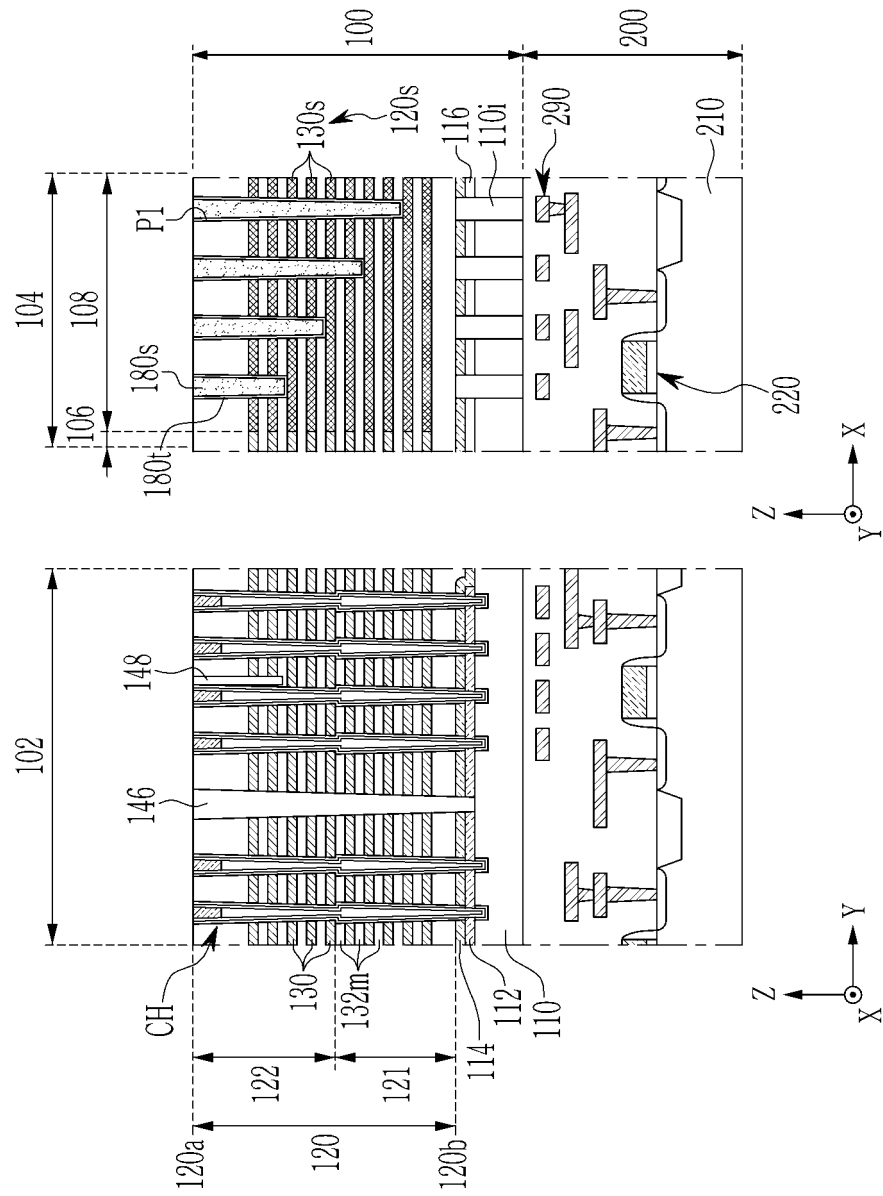


FIG. 13

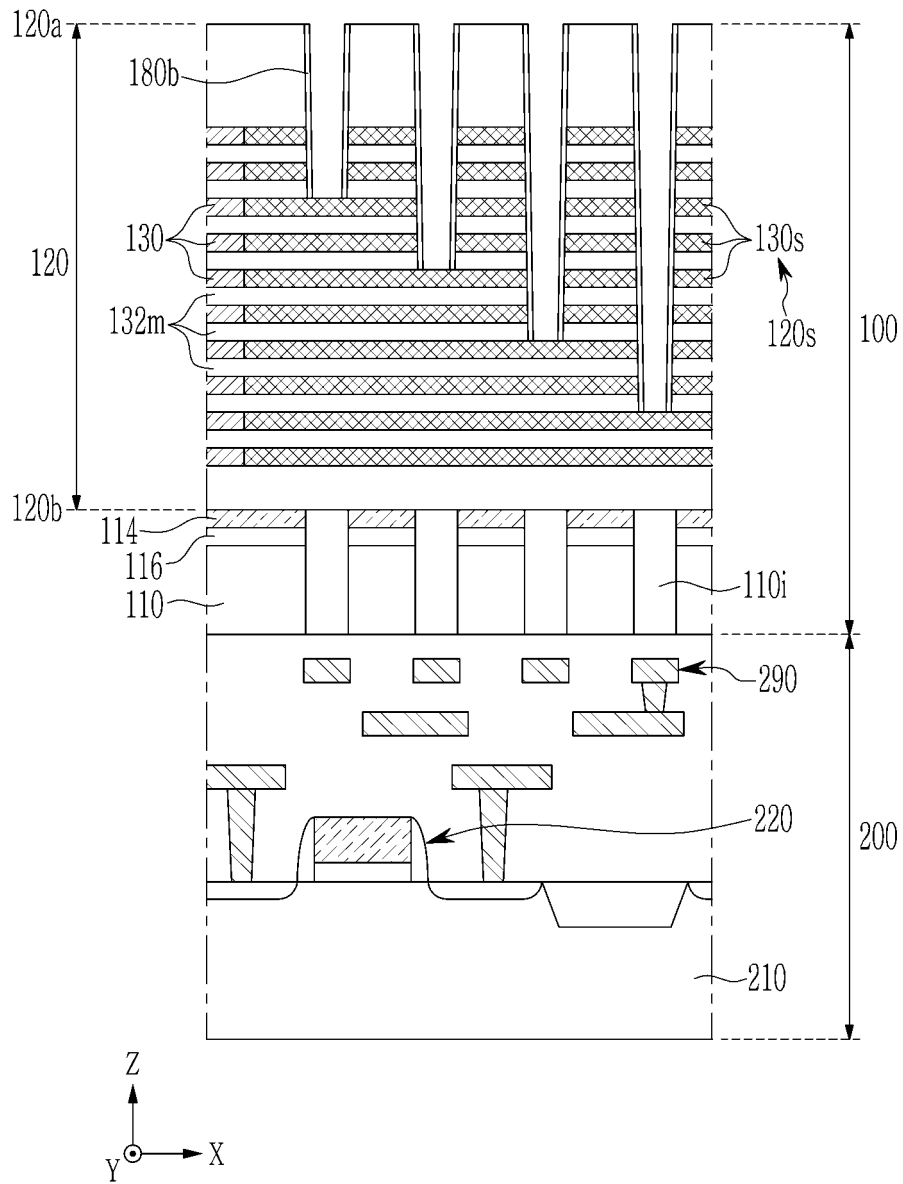


FIG. 14

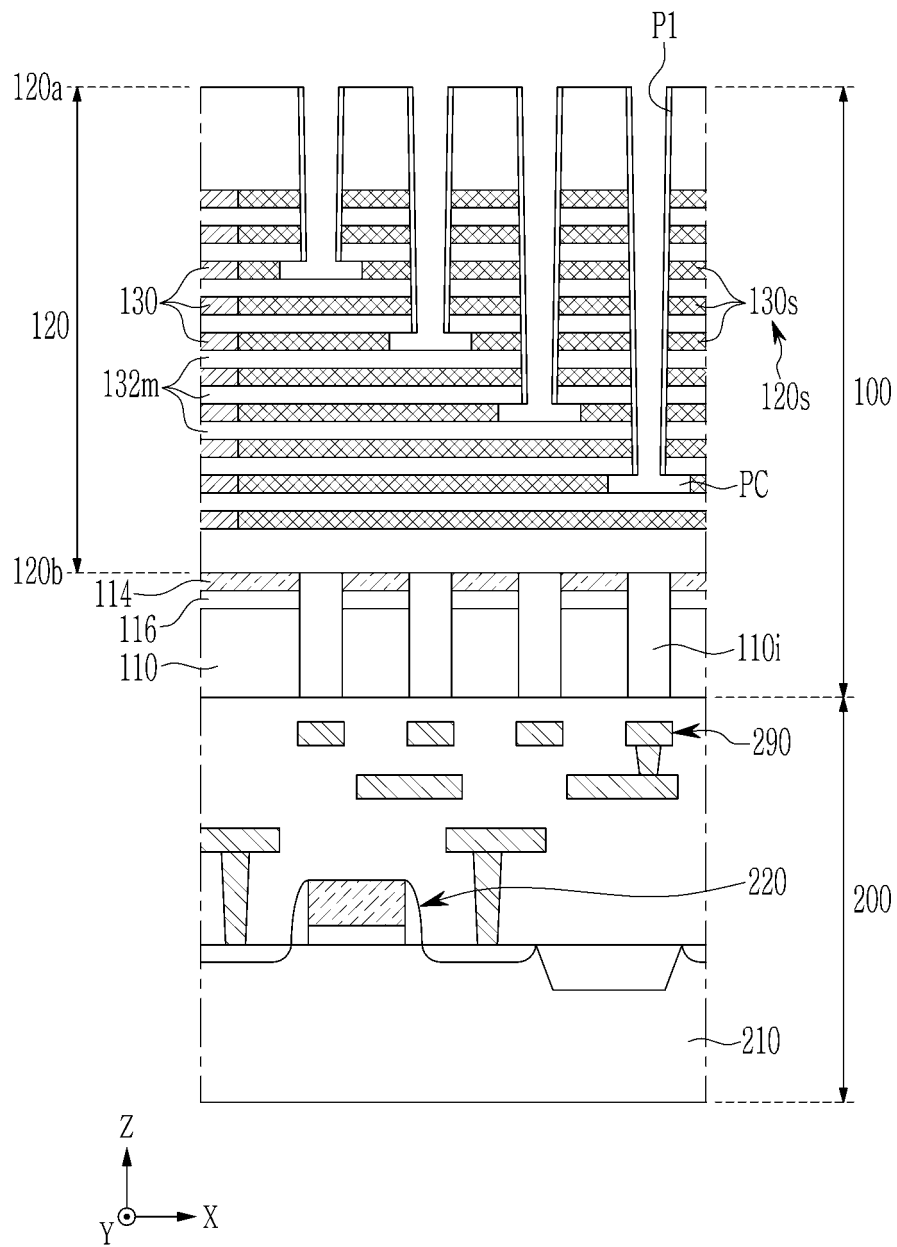


FIG. 15

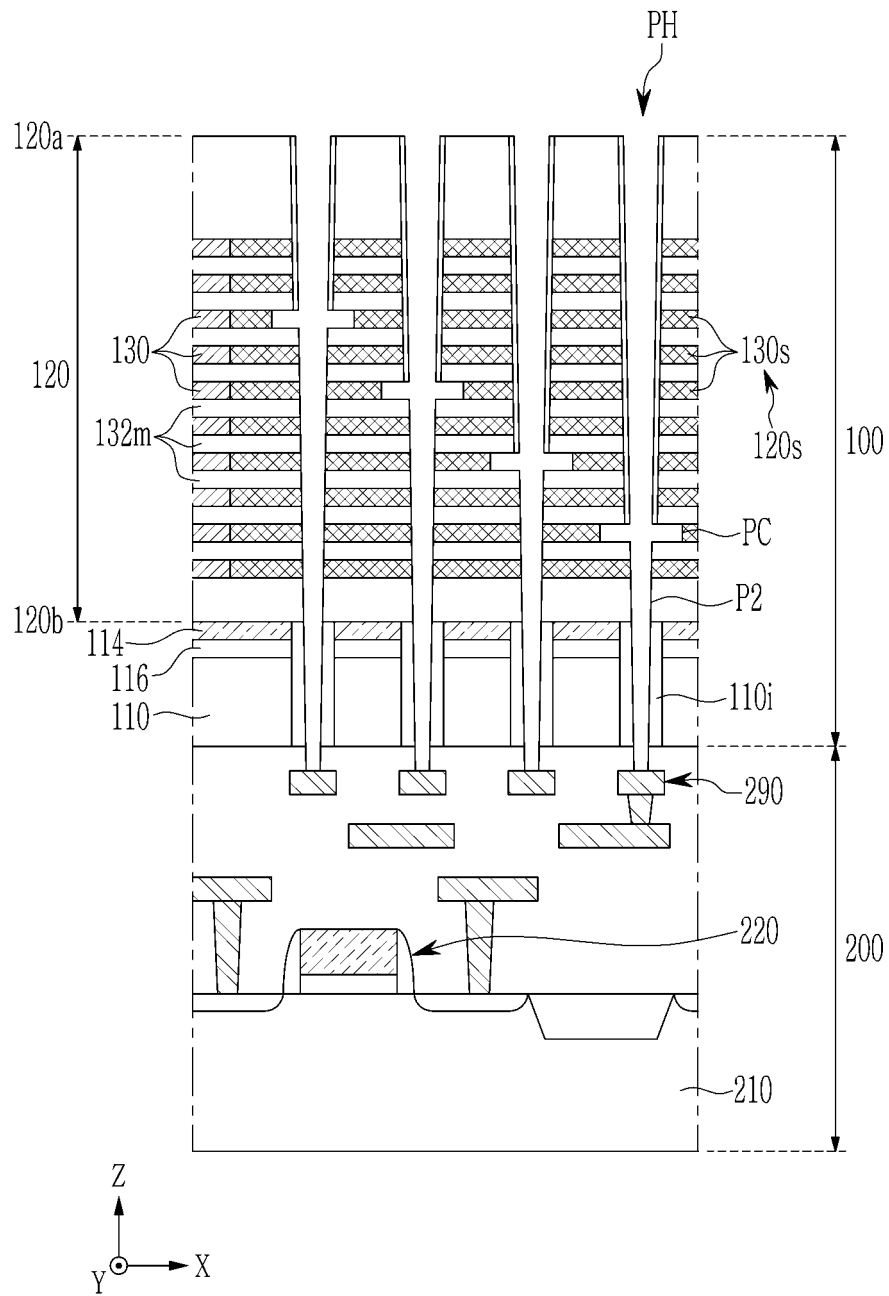


FIG. 16

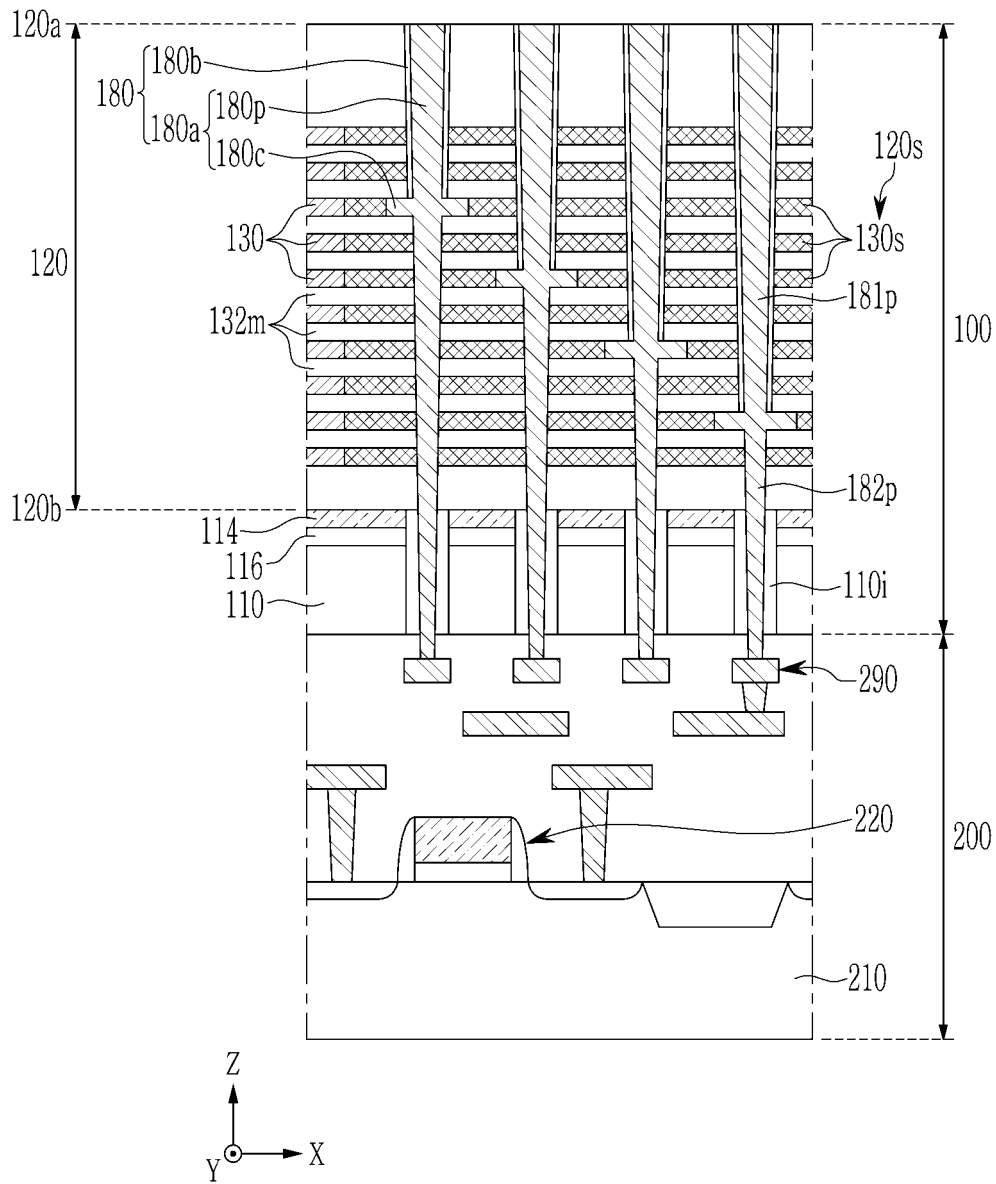


FIG. 17

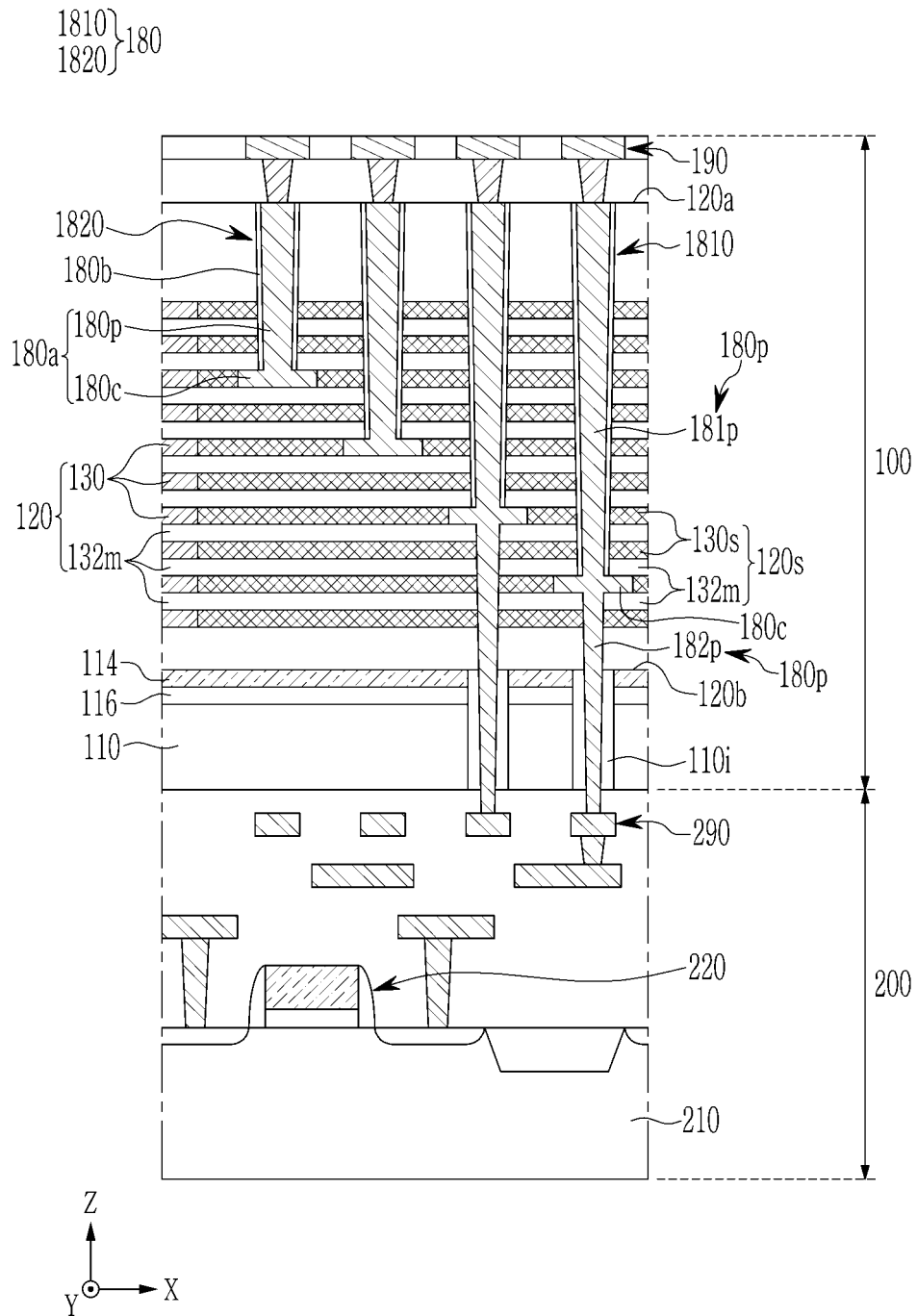


FIG. 18

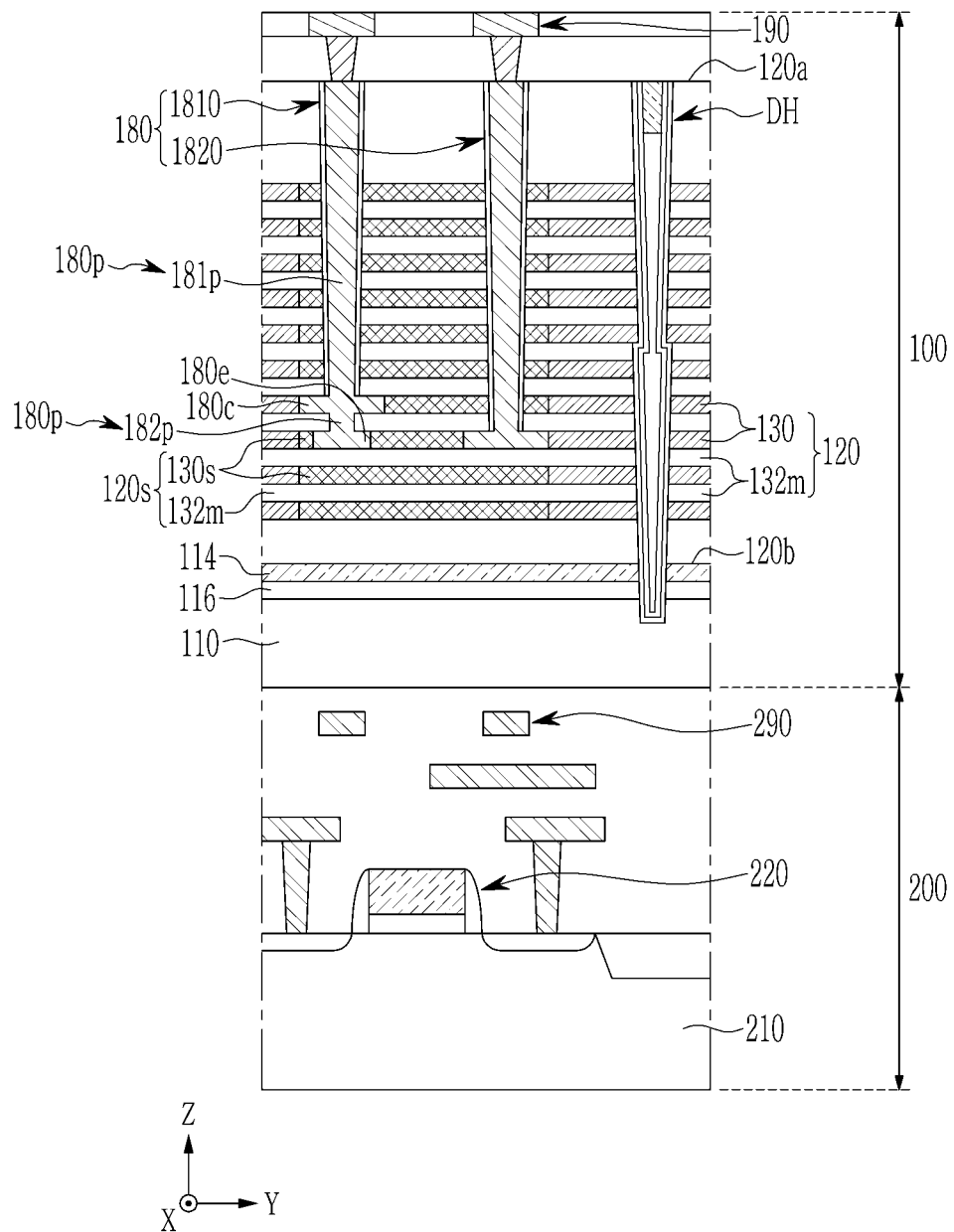


FIG. 19

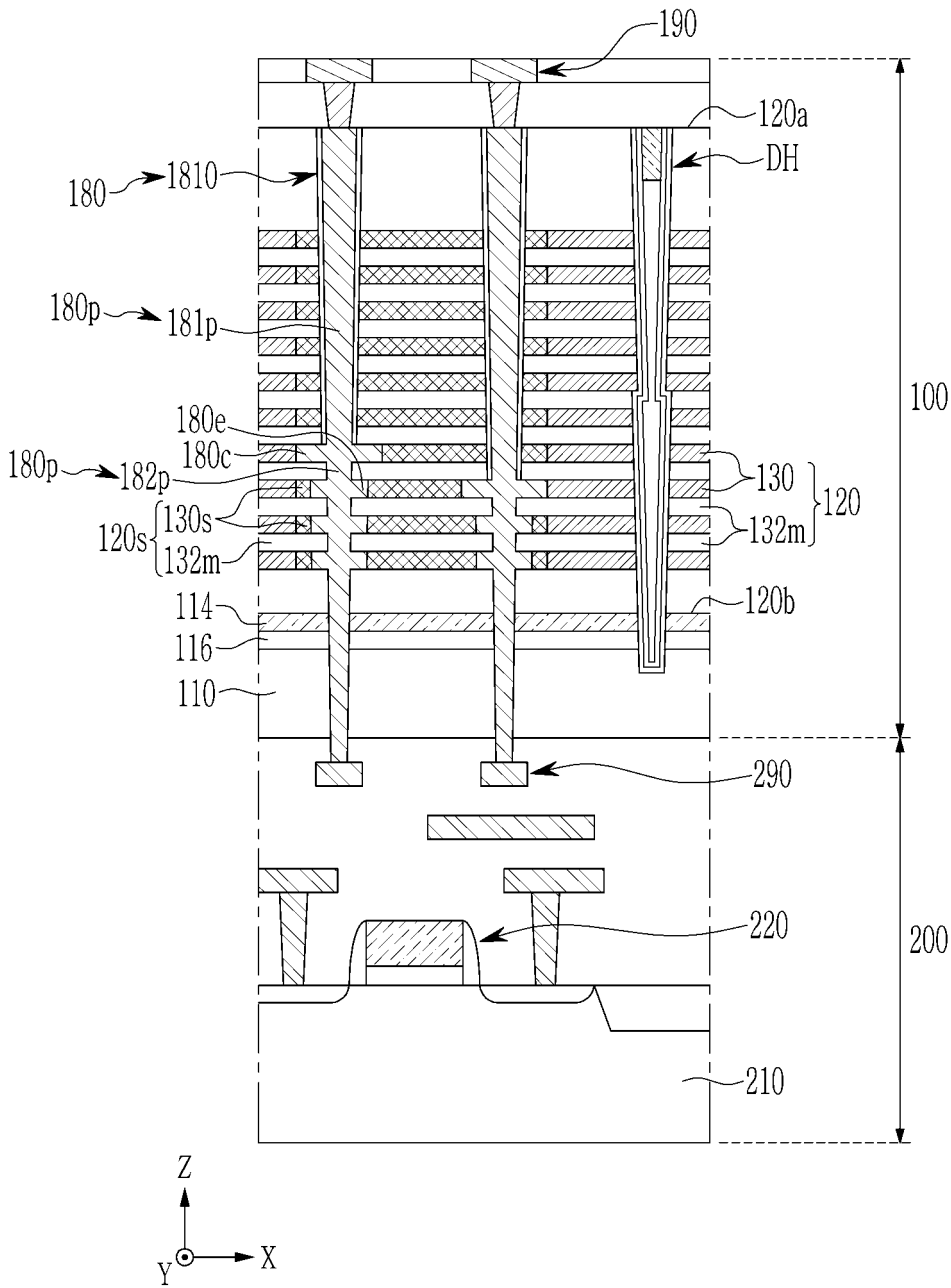


FIG. 20

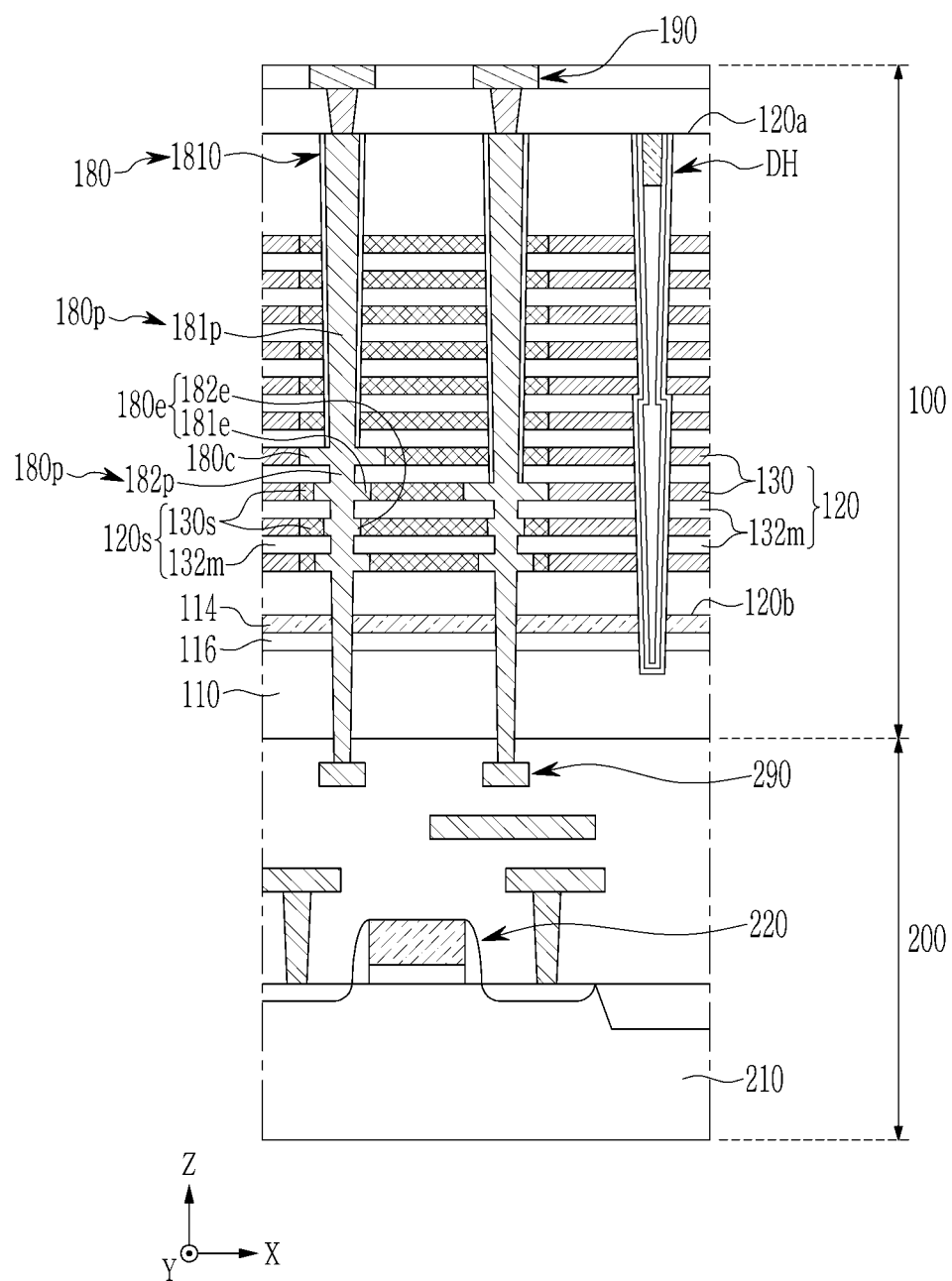


FIG. 21

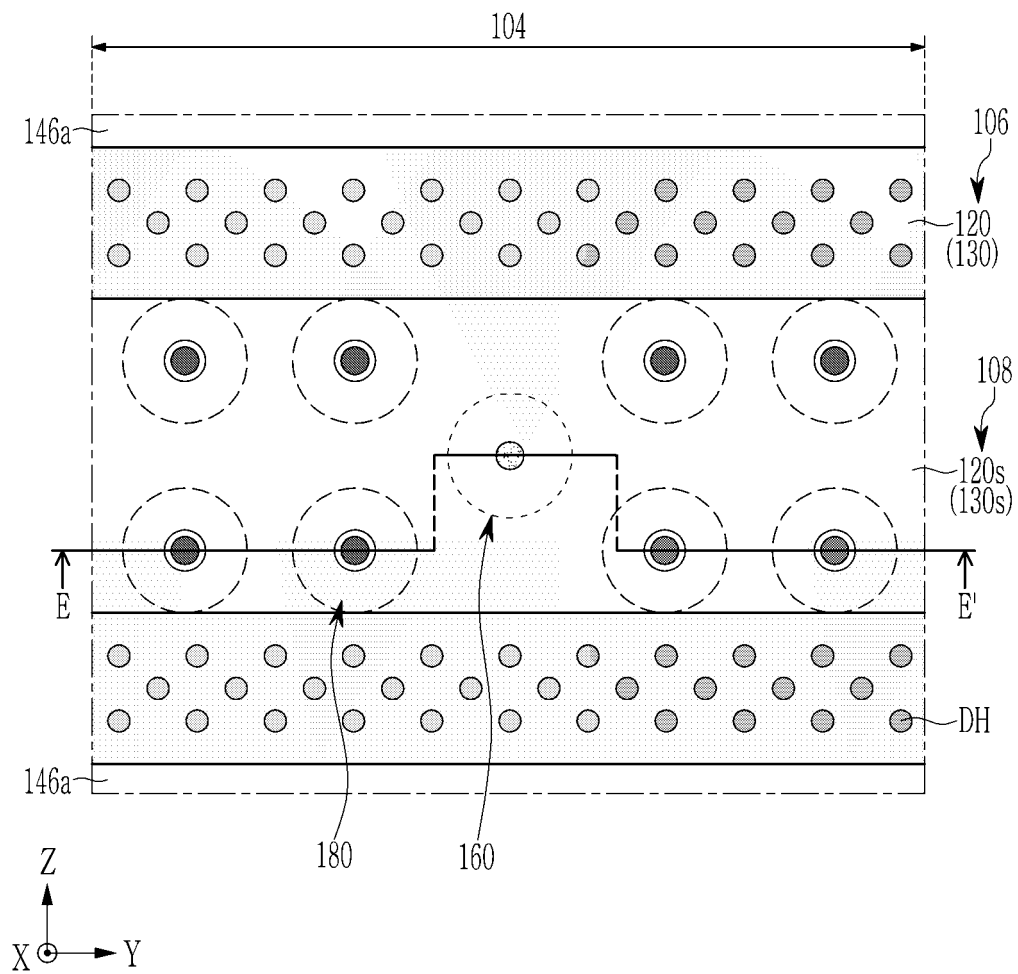


FIG. 22

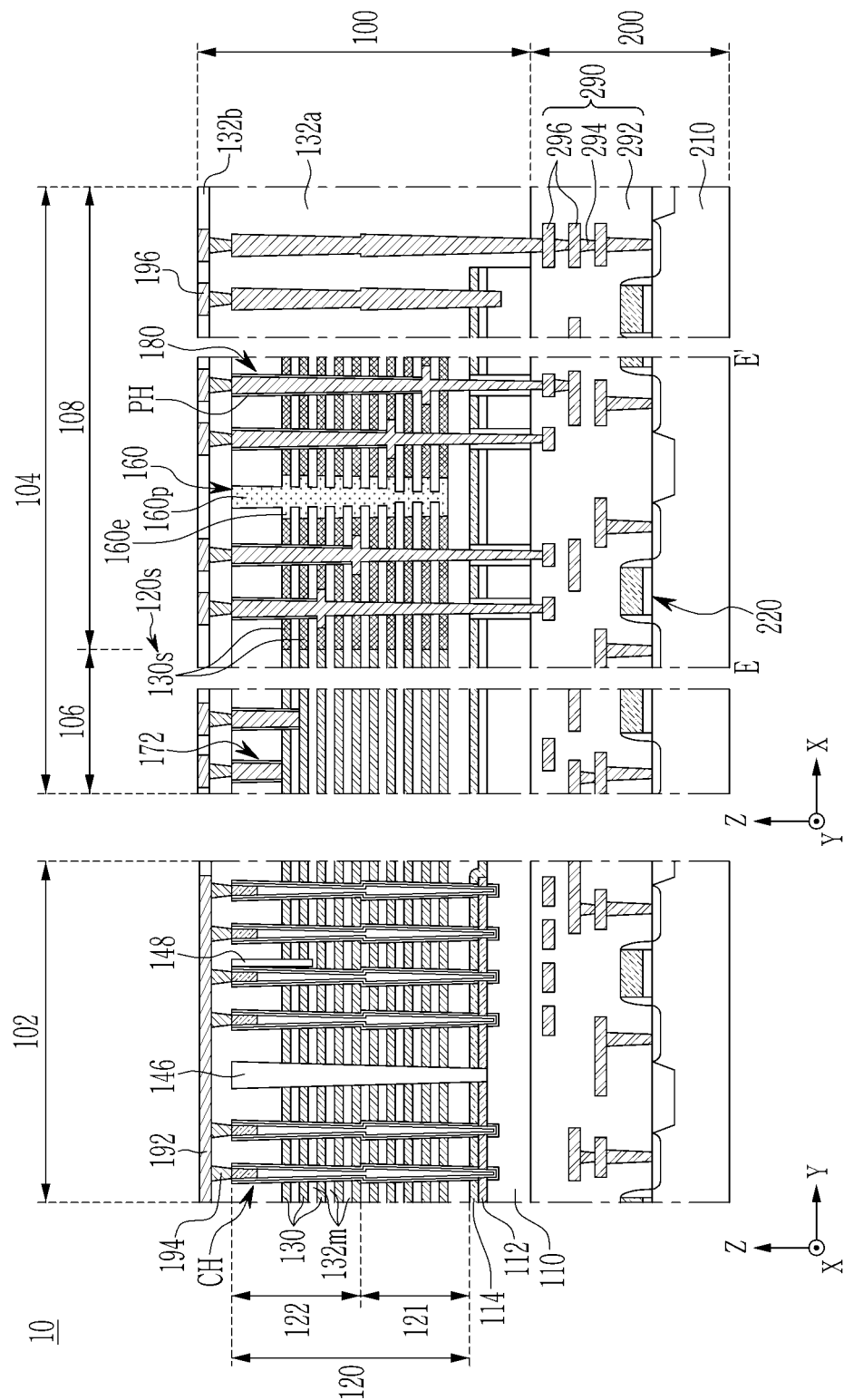


FIG. 23

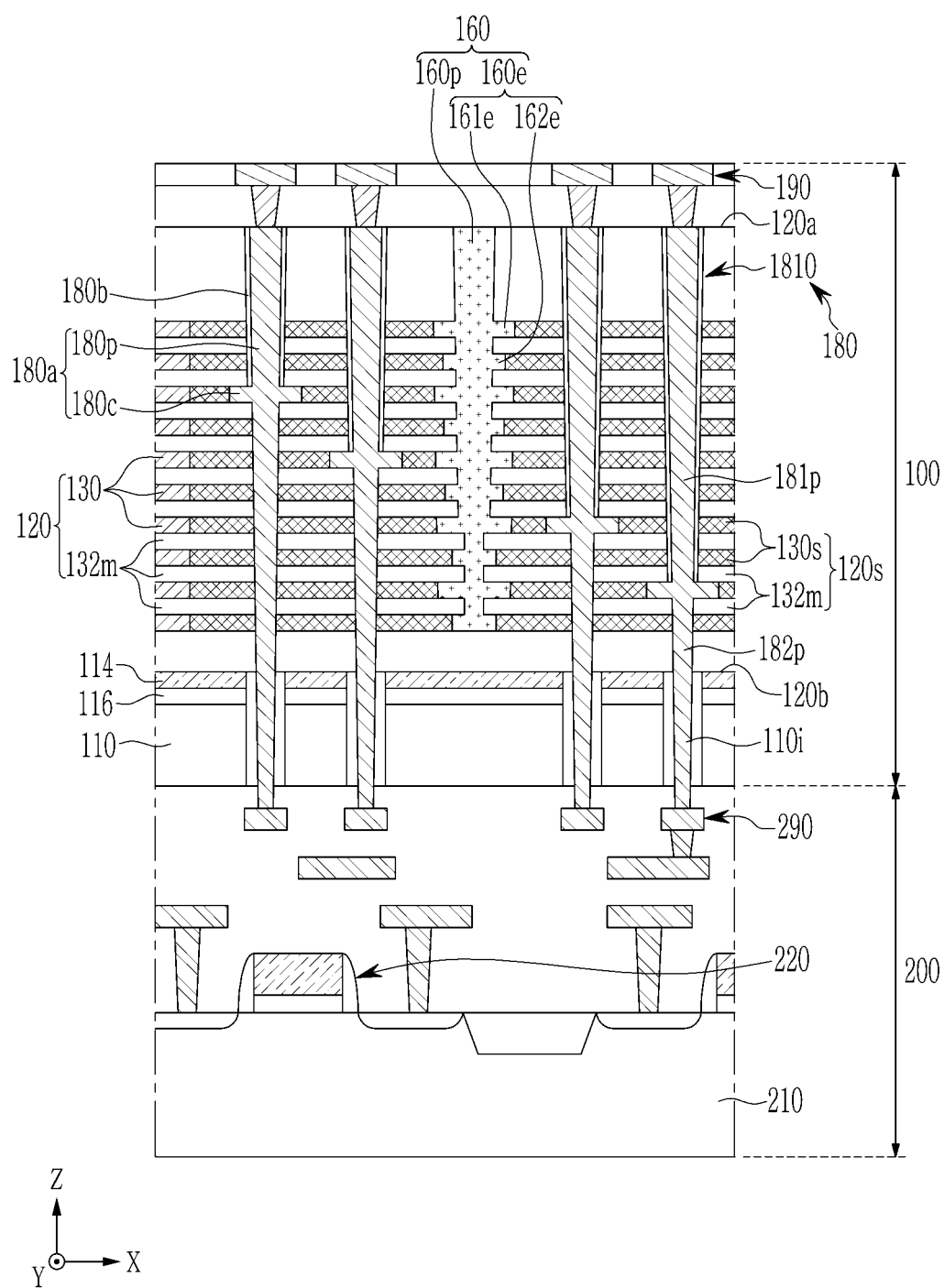
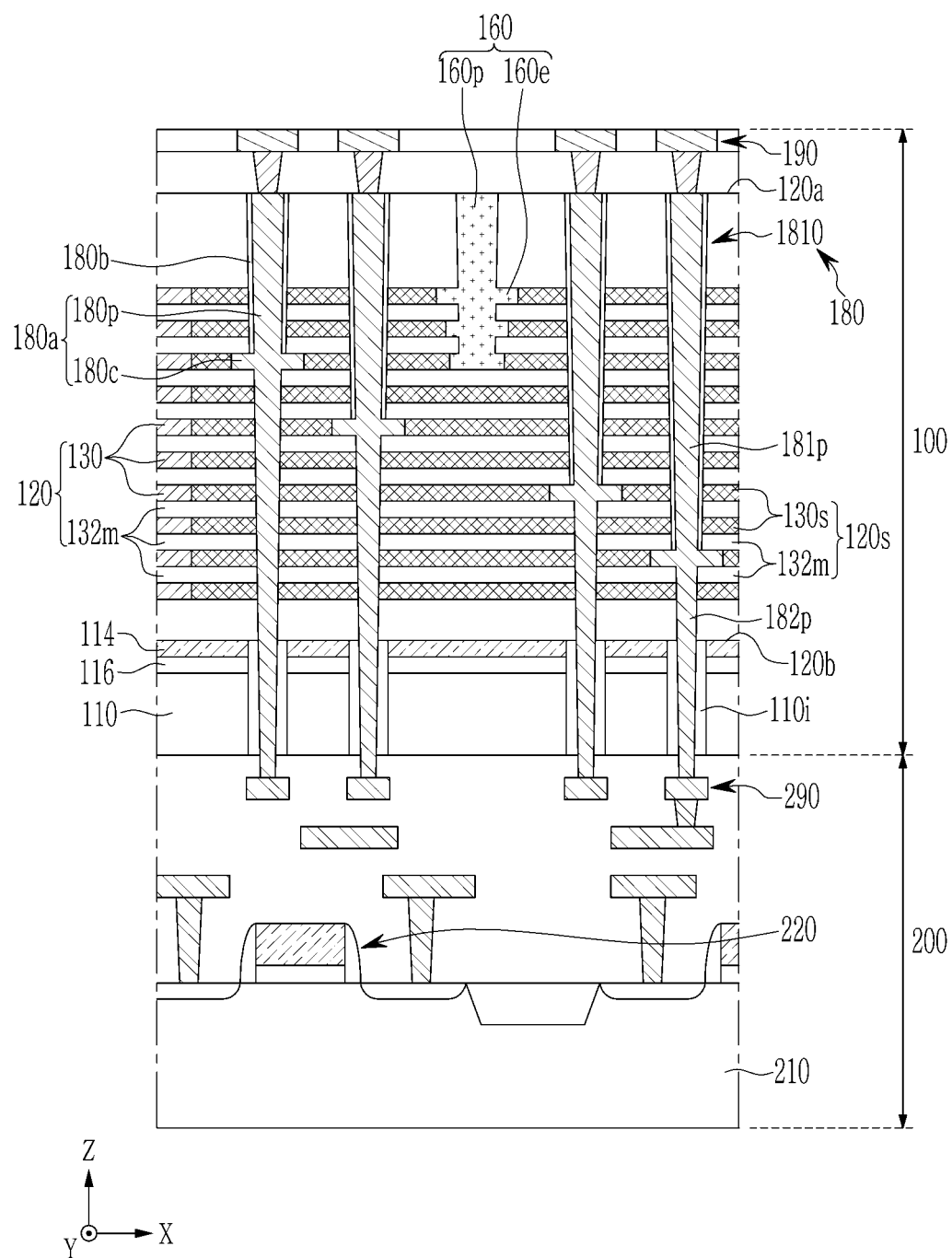


FIG. 24



$$\begin{array}{c} 160 \\ \hline 160p \quad 160e \end{array}$$


FIG. 26

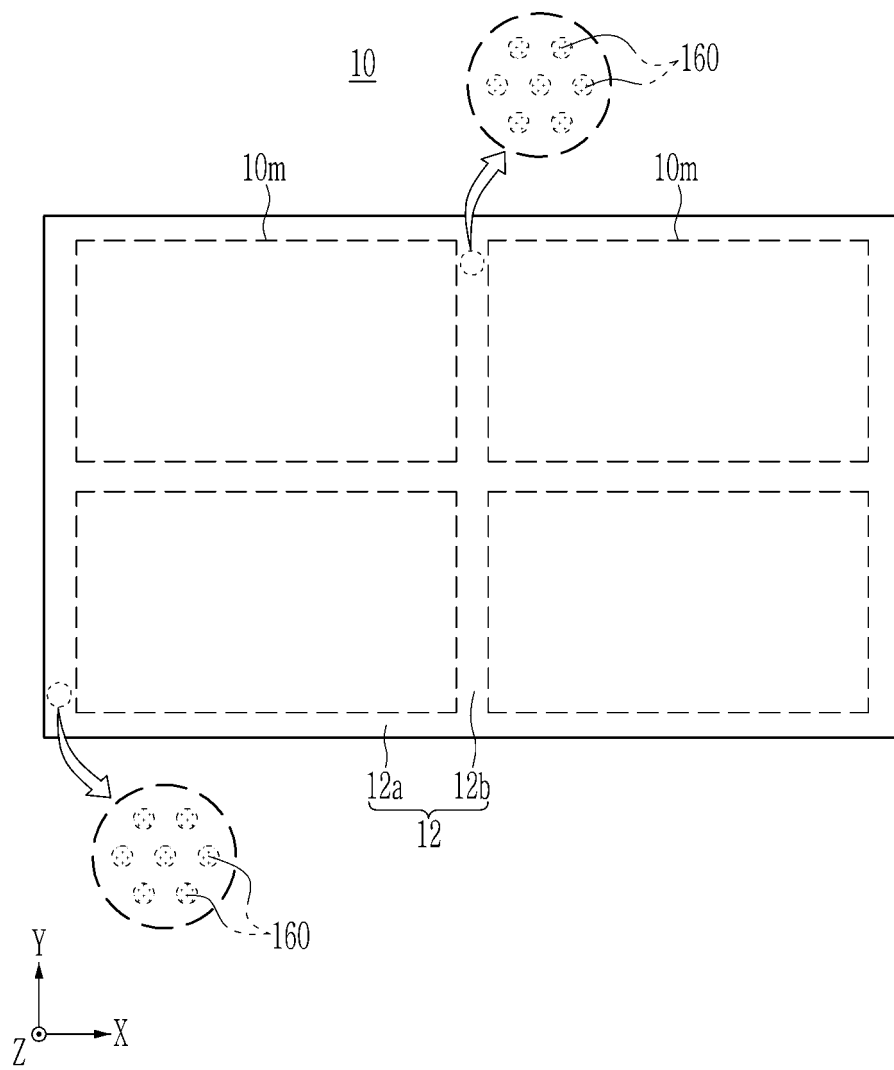


FIG. 27

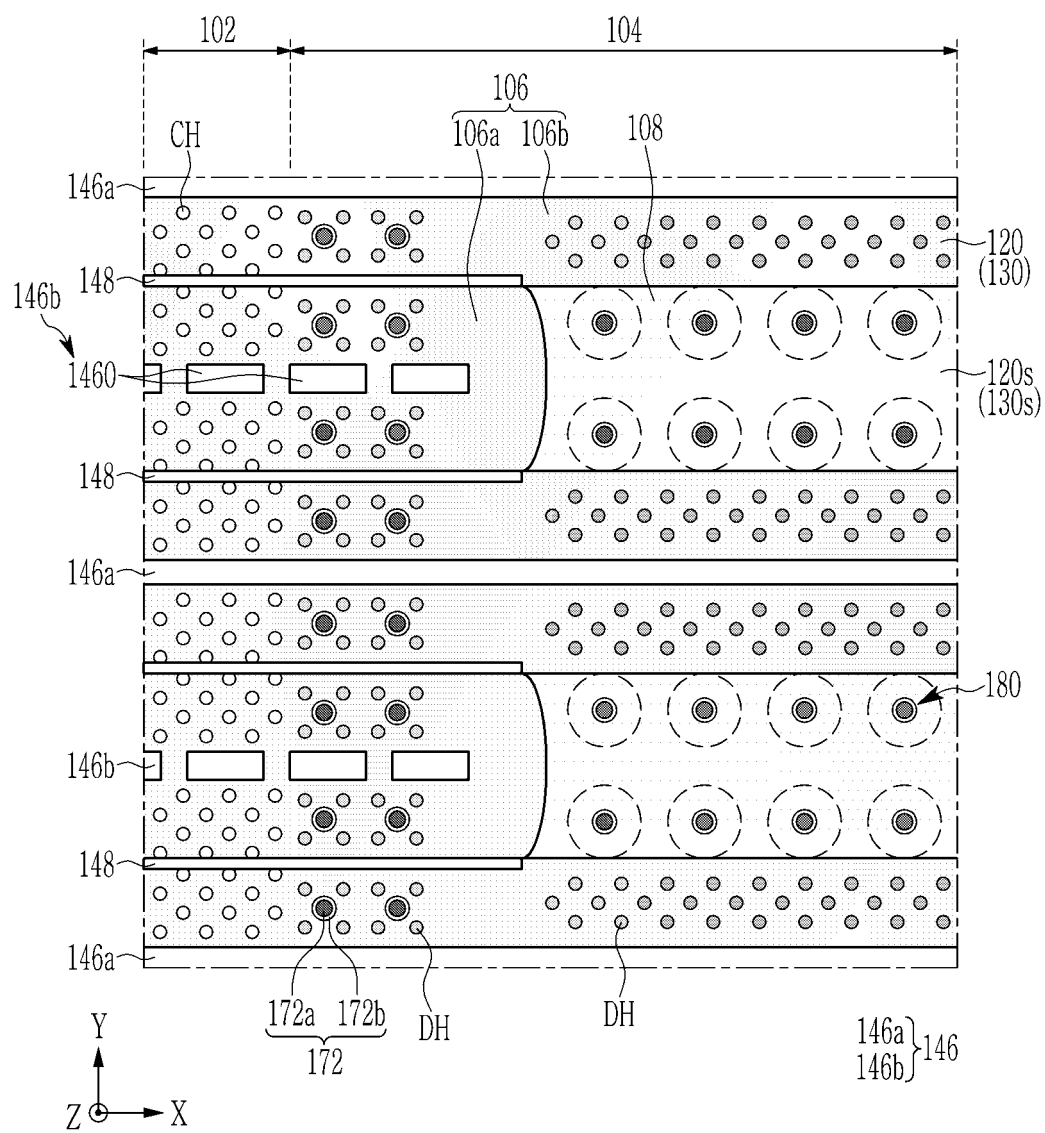


FIG. 28

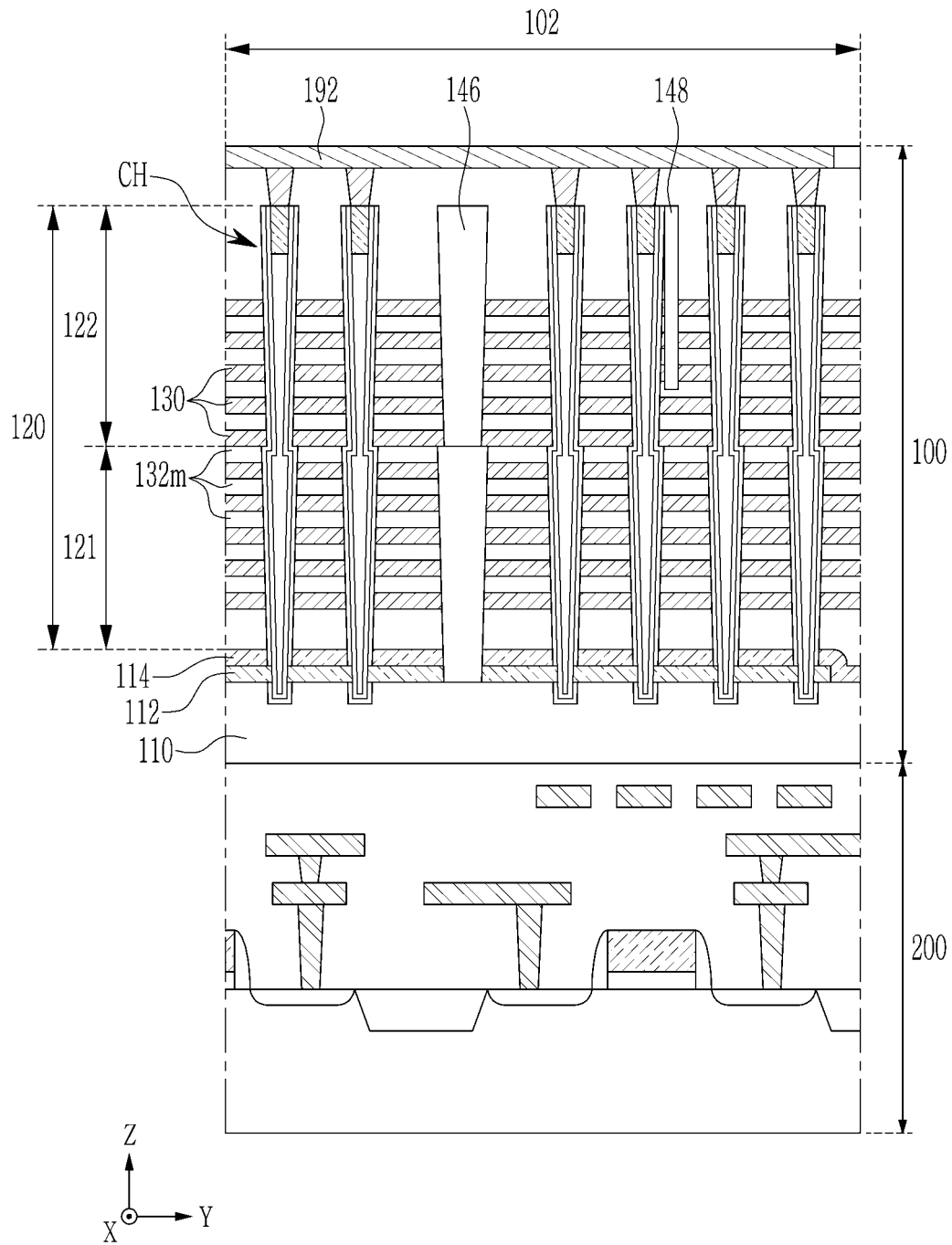


FIG. 29

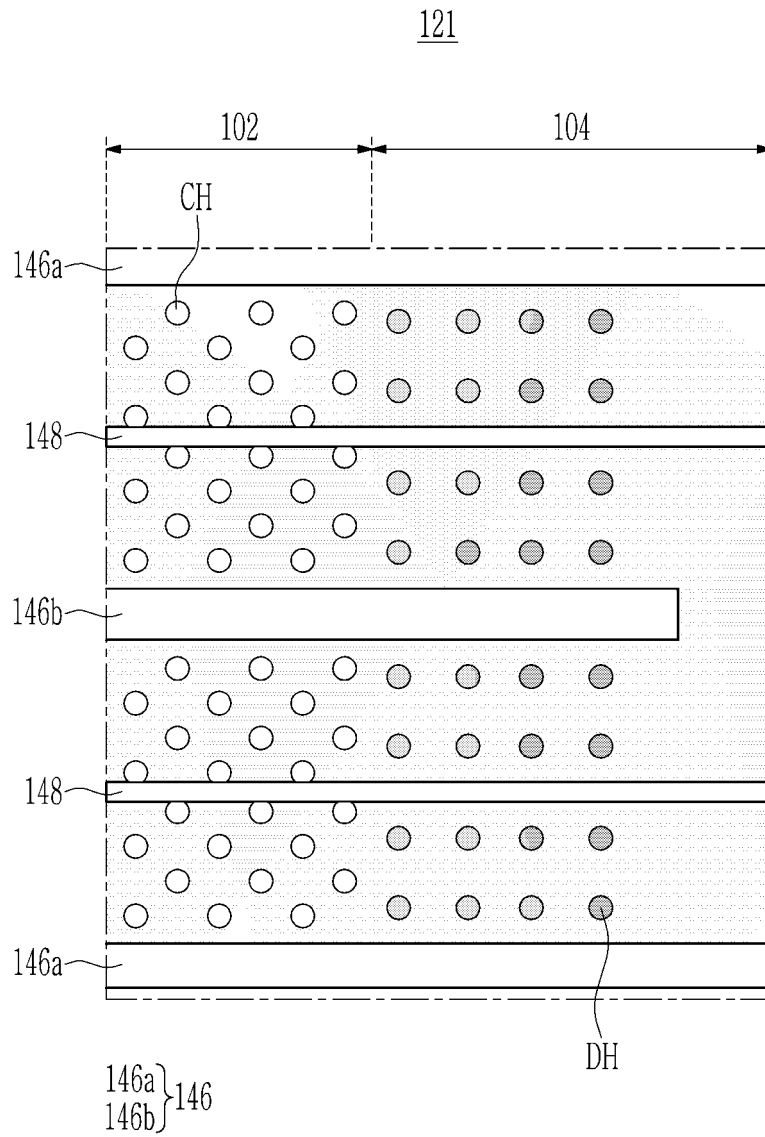


FIG. 30

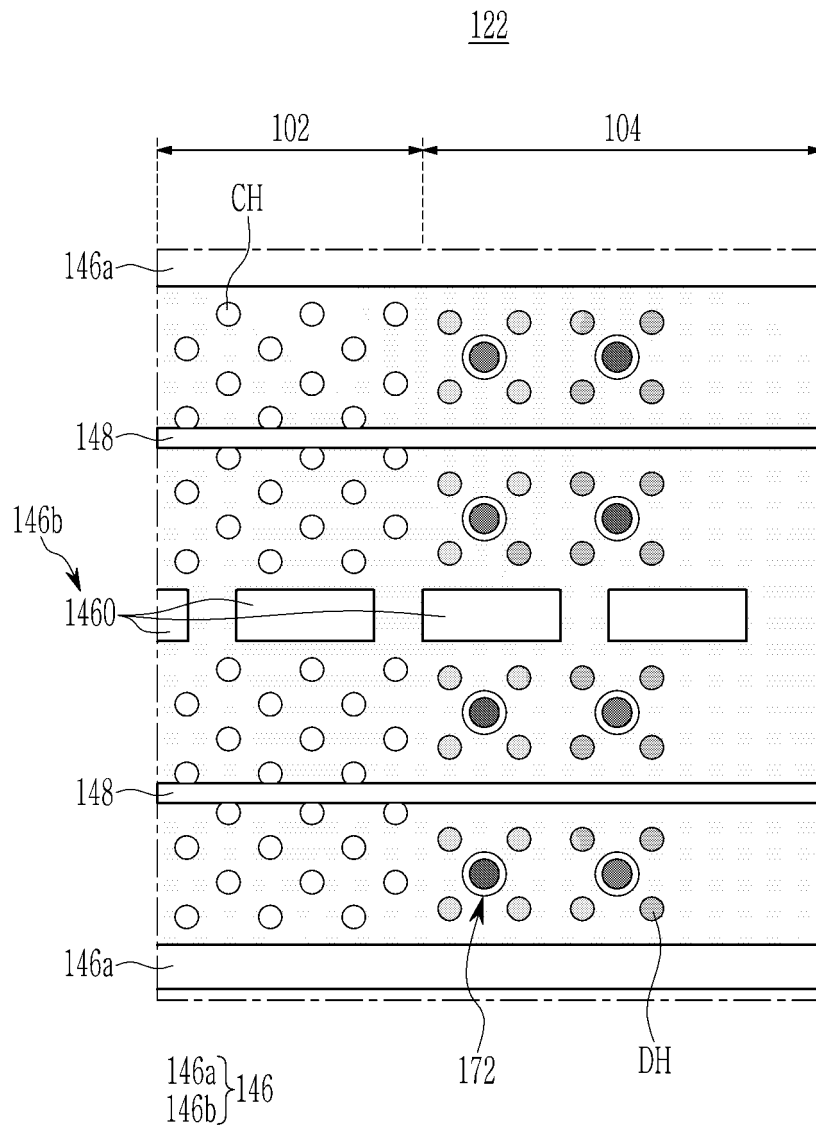


FIG. 31

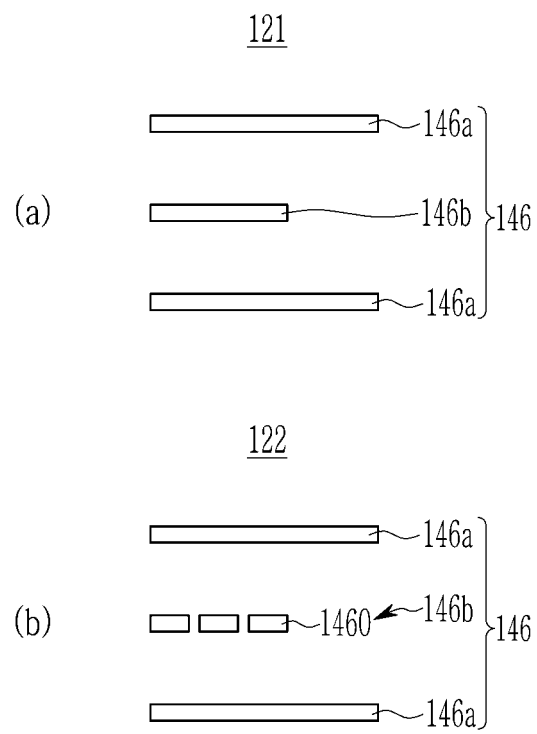


FIG. 32

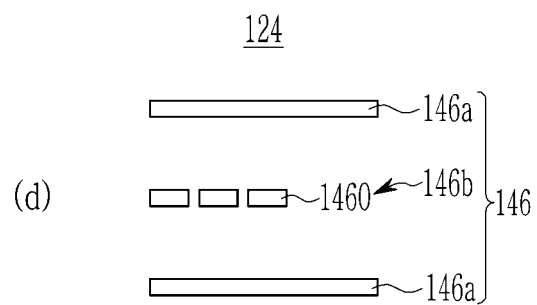
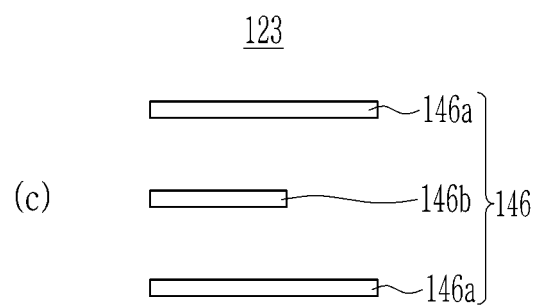
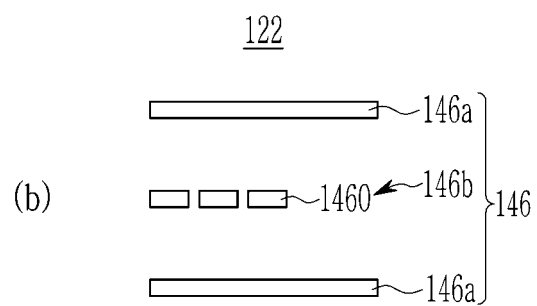
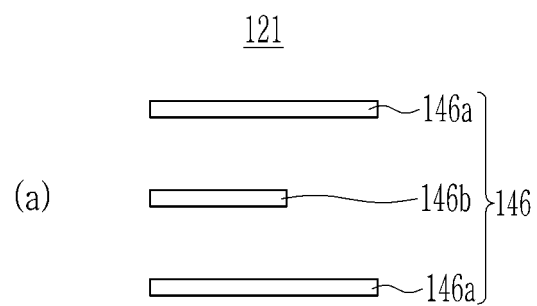


FIG. 33

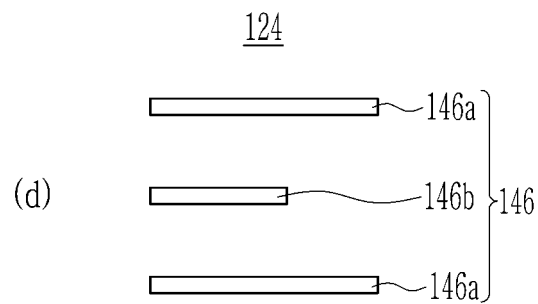
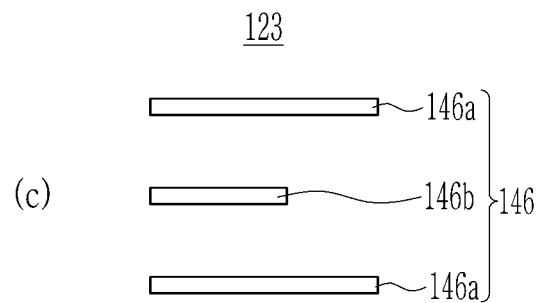
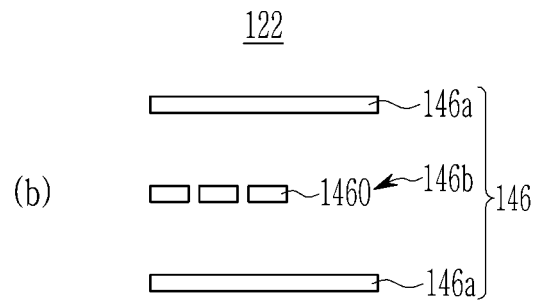
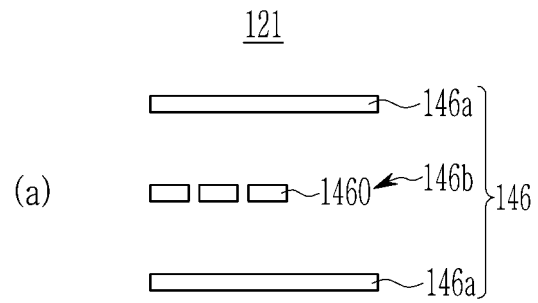


FIG. 34

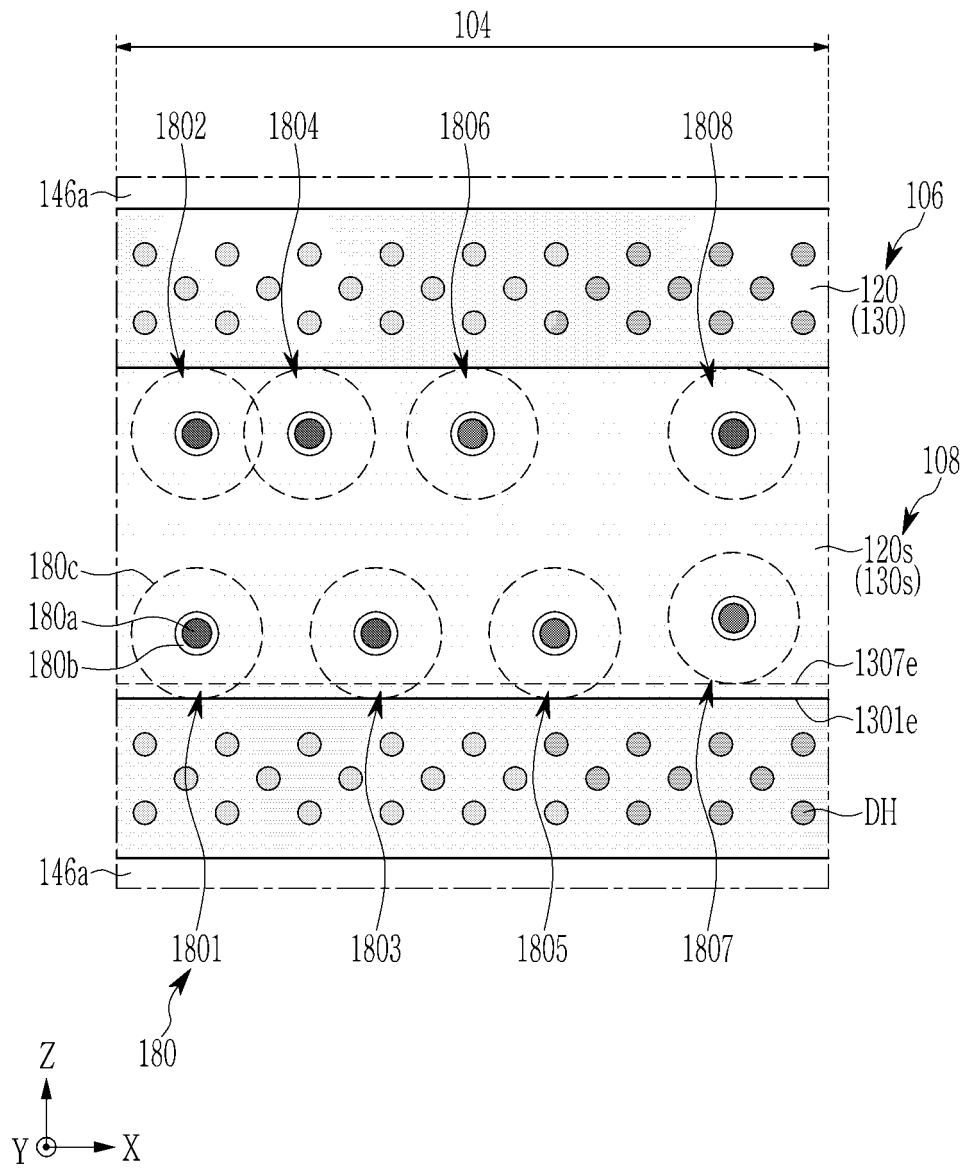


FIG. 36

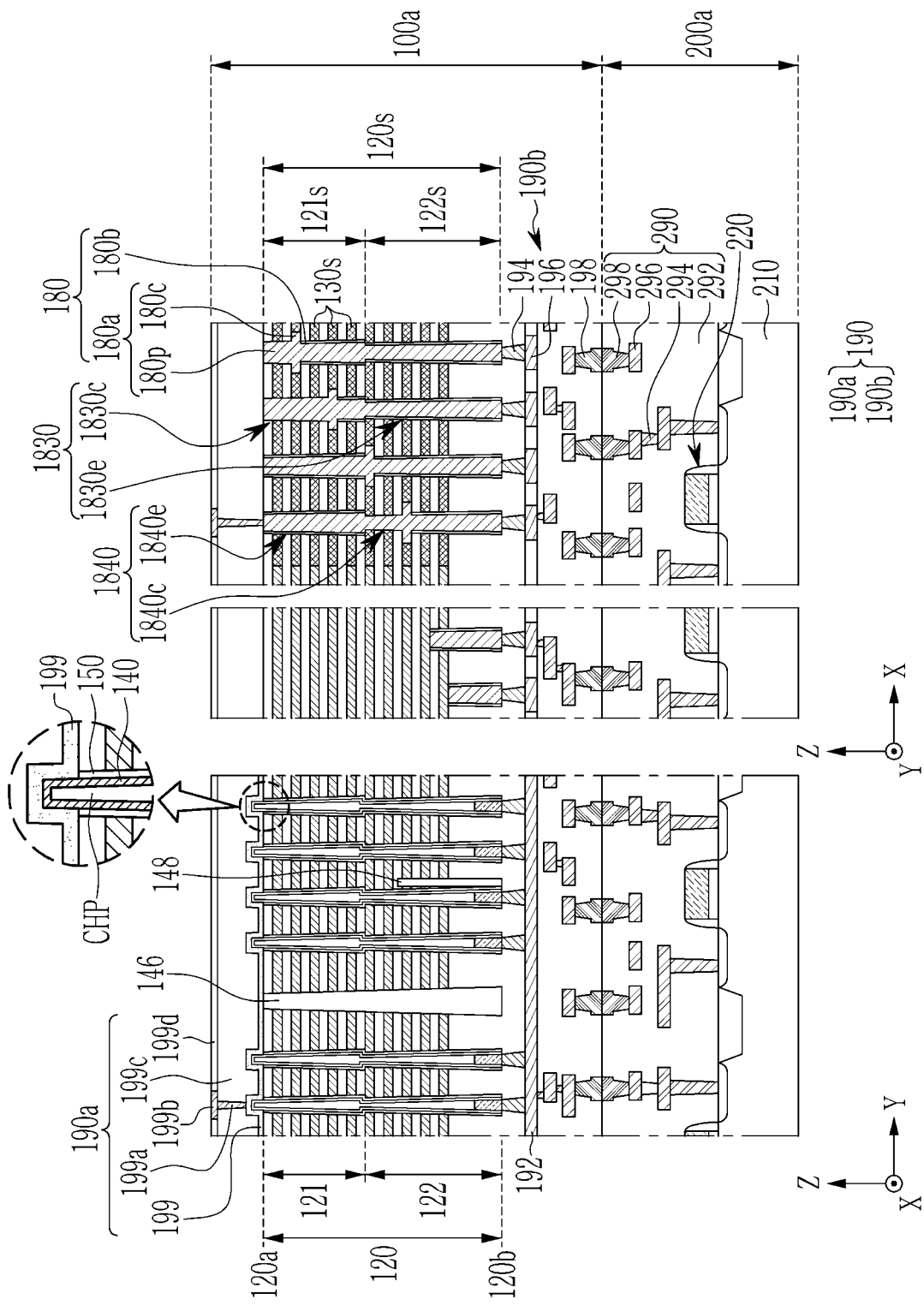


FIG. 37

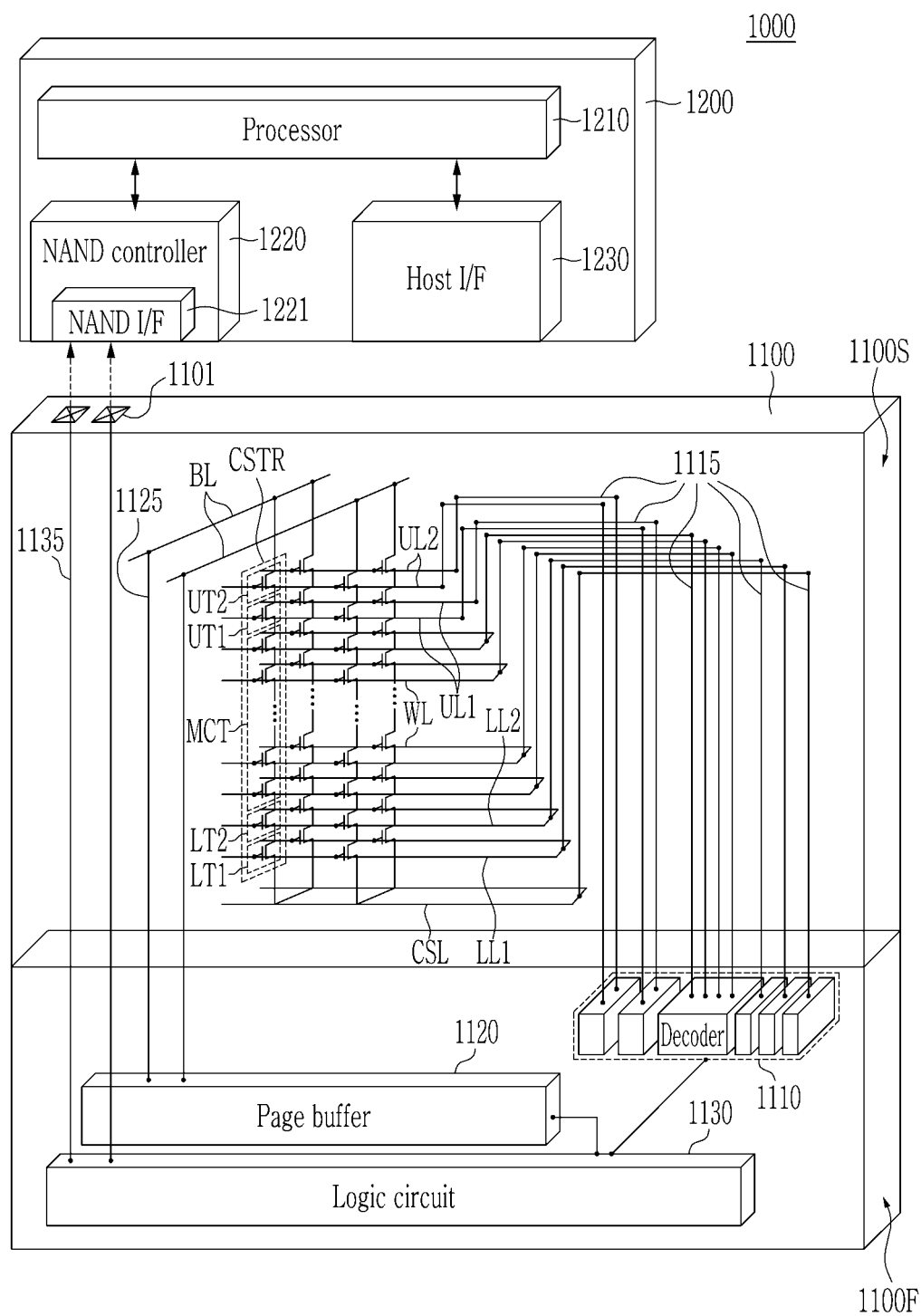


FIG. 38

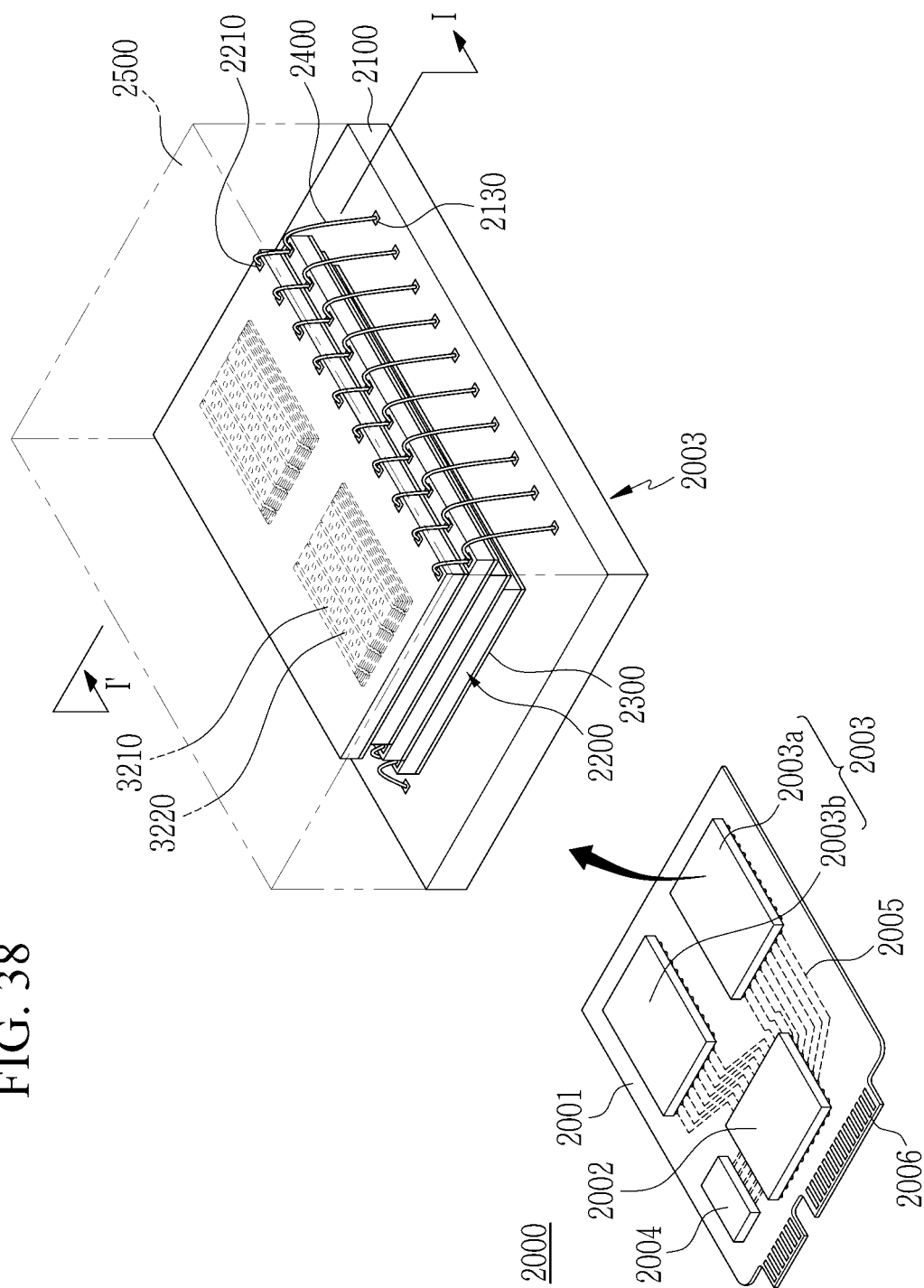


Figure 1 is a cross-sectional view of a semiconductor device. The device is divided into two main vertical sections: a top section 100 and a bottom section 200. The top section 100 has a total height of 104 and is divided into three horizontal regions with widths 106, 108, and 106. It contains a top layer 180 with sub-layers 180a, 180b, and 180c. A central vertical structure 120 is shown, with sub-layers 120a, 120b, and 120c. A central vertical channel 130 is also indicated. The bottom section 200 has a total height of 200 and contains a central vertical structure 220. The device is mounted on a substrate 210. A cross-sectional line I-I' is indicated at the bottom.

FIG. 40

